

# UCC53x0 シングル チャネル絶縁ゲート ドライバ

## 1 特長

- 機能オプション
  - 分割出力 (UCC53x0S)
  - GND2 を基準とする UVLO (UCC53x0E)
  - ミラー クランプ オプション (UCC53x0M)
- 8 ピン D (沿面距離 4mm) および DWV (沿面距離 8.5mm) パッケージ
- 60ns (代表値) の伝搬遅延時間
- 最小 CMTI: 100kV/ns
- 絶縁バリアの寿命: >40 年
- 入力電圧範囲: 3V~15V
- 最大 33V のドライバ電源電圧
  - 8V および 12V UVLO オプション
- 負の 5V に対応可能な入力ピン
- 安全関連認証:
  - DIN V VDE V 0884-11:2017-01 と DIN EN 61010-1 に準拠した絶縁耐圧: 7000V<sub>PK</sub> (DWV、予定)、4242V<sub>PK</sub> (D)
  - UL 1577 に準拠した絶縁耐圧定格 (1 分間): 5000V<sub>RMS</sub> (DWV)、3000V<sub>RMS</sub> (D)
  - GB4943.1-2011 準拠の CQC 認定: D および DWV (予定)
- CMOS 入力
- 動作温度: -40°C~+125°C

## 2 アプリケーション

- モータドライブ
- 高電圧の DC/DC コンバータ
- UPS および PSU
- HEV および EV 電源モジュール
- 太陽光インバータ

## 3 概要

UCC53x0 は、MOSFET、IGBT、SiC MOSFET、GaN FET (UCC5350SBD) を駆動するように設計されたシングル チャネル絶縁型ゲート ドライバのファミリです。UCC53x0S には分割出力があり、立ち上がりと立ち下りの時間を別々に制御できます。UCC53x0M は、トランジスタのゲートを内部的なクランプへ接続することで、ミラー電流により誤って電源オンが発生することを防止します。UCC53x0E には、GND2 を基準とする UVLO2 があり、真の UVLO 読み取り値を得られます。

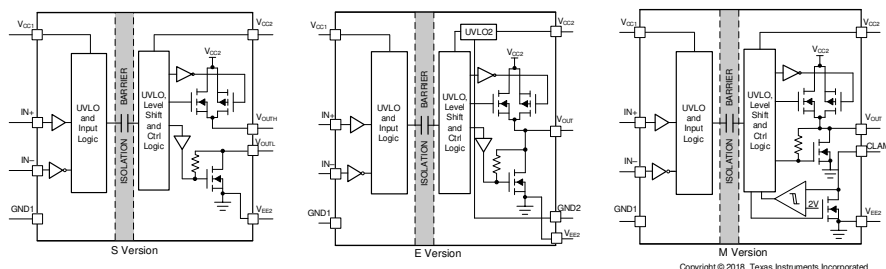
UCC53x0 は、4mm SOIC-8 (D) または 8.5mm SOIC-8 (DWV) パッケージで供給され、それぞれ最大 3kV<sub>RMS</sub> および 5kV<sub>RMS</sub> の絶縁電圧をサポートできます。これらの各種のオプションを取りそろえた UCC53x0 ファミリは、モータドライブや産業用電源に適しています。

フォトカプラと比較して、UCC53x0 ファミリは部品間スキューが小さく、伝搬遅延時間が短く、より高い温度でも動作し、CMTI が高いという特長があります。

### 製品情報

発注用製品型番 (1) (2)	最小のソースおよびシンク電流	説明
UCC5310MC	2.4A, 1.1A	ミラー クランプ
UCC5320SC	2.4A, 2.2A	分割出力
UCC5320EC	2.4A, 2.2A	IGBT エミッタを基準とする UVLO
UCC5350MC	5A, 5A	ミラー クランプ
UCC5350SB	5A, 5A	8V UVLO 付きの分割出力
UCC5390SC	10A, 10A	分割出力
UCC5390EC	10A, 10A	IGBT エミッタを基準とする UVLO

- 供給されているすべてのパッケージについては、[セクション 14](#) を参照してください。
- デバイスの詳細な比較については、[セクション 4](#) を参照してください。



機能ブロック図 (S、E、M バージョン)



## Table of Contents

<b>1 特長</b> .....	1	8.1 Overview.....	25
<b>2 アプリケーション</b> .....	1	8.2 Functional Block Diagram.....	25
<b>3 概要</b> .....	1	8.3 Feature Description.....	27
<b>4 Device Comparison Table</b> .....	3	8.4 Device Functional Modes.....	31
<b>5 Pin Configuration and Function</b> .....	4	<b>9 Application and Implementation</b> .....	33
<b>6 Specifications</b> .....	6	9.1 Application Information.....	33
6.1 Absolute Maximum Ratings.....	6	9.2 Typical Application.....	33
6.2 ESD Ratings.....	6	<b>10 Power Supply Recommendations</b> .....	39
6.3 Recommended Operating Conditions.....	6	<b>11 Layout</b> .....	40
6.4 Thermal Information.....	7	11.1 Layout Guidelines.....	40
6.5 Power Ratings.....	7	11.2 Layout Example.....	41
6.6 Insulation Specifications for D Package.....	8	11.3 PCB Material.....	42
6.7 Insulation Specifications for DWV Package.....	9	<b>12 Device and Documentation Support</b> .....	44
6.8 Safety-Related Certifications For D Package.....	10	12.1 Device Support.....	44
6.9 Safety-Related Certifications For DWV Package.....	10	12.2 Documentation Support.....	44
6.10 Safety Limiting Values.....	10	12.3 Certifications.....	44
6.11 Electrical Characteristics.....	11	12.4 ドキュメントの更新通知を受け取る方法.....	44
6.12 Switching Characteristics.....	13	12.5 サポート・リソース.....	44
6.13 Insulation Characteristics Curves.....	14	12.6 Trademarks.....	44
6.14 Typical Characteristics.....	15	12.7 静電気放電に関する注意事項.....	44
<b>7 Parameter Measurement Information</b> .....	22	12.8 用語集.....	44
7.1 Propagation Delay, Inverting, and Noninverting Configuration.....	22	<b>13 Revision History</b> .....	44
<b>8 Detailed Description</b> .....	25	<b>14 Mechanical, Packaging, and Orderable Information</b> .....	46

## 4 Device Comparison Table

DEVICE OPTION <sup>(1)</sup>	PACKAGE	MINIMUM SOURCE CURRENT	MINIMUM SINK CURRENT	PIN CONFIGURATION	UVLO	ISOLATION RATING
UCC5310MC	D	2.4 A	1.1 A	Miller clamp	12 V	3-kV <sub>RMS</sub>
	DWV					5-kV <sub>RMS</sub>
UCC5320EC	D	2.4 A	2.2 A	UVLO with reference to GND2	12 V	3-kV <sub>RMS</sub>
UCC5320SC	D	2.4 A	2.2 A	Split output	12 V	3-kV <sub>RMS</sub>
	DWV					5-kV <sub>RMS</sub>
UCC5350MC	D	5 A	5 A	Miller clamp	12 V	3-kV <sub>RMS</sub>
	DWV					5-kV <sub>RMS</sub>
UCC5350SB	D	5 A	5 A	Split Output	8 V	3-kV <sub>RMS</sub>
UCC5390EC	D	10 A	10 A	UVLO with reference to GND2	12 V	3-kV <sub>RMS</sub>
	DWV					5-kV <sub>RMS</sub>
UCC5390SC	D	10 A	10 A	Split output	12 V	3-kV <sub>RMS</sub>

(1) The S, E, and M suffixes are part of the orderable part number. See [セクション 14](#) for the full orderable part number.

## 5 Pin Configuration and Function

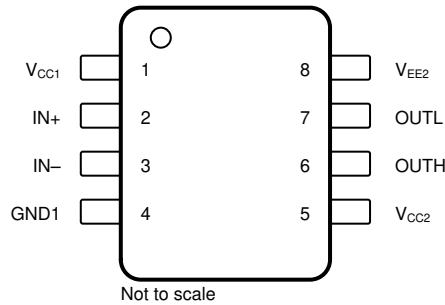


図 5-1. UCC5320S, UCC5350SB, and UCC5390S 8-Pin SOIC Top View

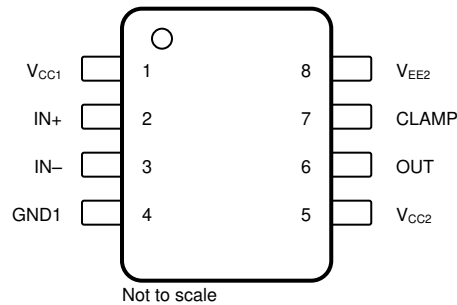


図 5-2. UCC5310M and UCC5350M 8-Pin SOIC Top View

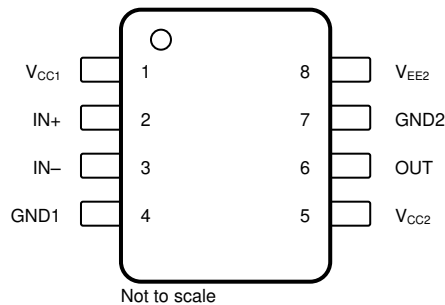


図 5-3. UCC5320E and UCC5390E 8-Pin SOIC Top View

表 5-1. Pin Functions

NAME	PIN			TYPE <sup>(1)</sup>	DESCRIPTION
	NO.				
	UCC53x0S	UCC53x0M	UCC53x0E		
CLAMP	—	7	—	I	Active Miller-clamp input found on the UCC53x0M used to prevent false turnon of the power switches.
GND1	4	4	4	G	Input ground. All signals on the input side are referenced to this ground.
GND2	—	—	7	G	Gate-drive common pin. Connect this pin to the IGBT emitter. UVLO referenced to GND2 in the UCC53x0E.
IN+	2	2	2	I	Noninverting gate-drive voltage-control input. The IN+ pin has a CMOS input threshold. This pin is pulled low internally if left open. Use 表 8-4 to understand the input and output logic of these devices.
IN-	3	3	3	I	Inverting gate-drive voltage control input. The IN- pin has a CMOS input threshold. This pin is pulled high internally if left open. Use 表 8-4 to understand the input and output logic of these devices.
OUT	—	6	6	O	Gate-drive output for UCC53x0E and UCC53x0M versions.

**表 5-1. Pin Functions (続き)**

NAME	PIN			TYPE <sup>(1)</sup>	DESCRIPTION
	NO.				
	UCC53x0S	UCC53x0M	UCC53x0E		
OUTH	6	—	—	O	Gate-drive pull-up output found on the UCC53x0S.
OUTL	7	—	—	O	Gate-drive pull-down output found on the UCC53x0S.
V <sub>CC1</sub>	1	1	1	P	Input supply voltage. Connect a locally decoupled capacitor to GND. Use a low-ESR or ESL capacitor located as close to the device as possible.
V <sub>CC2</sub>	5	5	5	P	Positive output supply rail. Connect a locally decoupled capacitor to V <sub>EE2</sub> . Use a low-ESR or ESL capacitor located as close to the device as possible.
V <sub>EE2</sub>	8	8	8	P	Negative output supply rail for E version, and GND for S and M versions. Connect a locally decoupled capacitor to GND2 for E version. Use a low-ESR or ESL capacitor located as close to the device as possible.

(1) P = Power, G = Ground, I = Input, O = Output

## 6 Specifications

### 6.1 Absolute Maximum Ratings

Over operating free air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT
Input bias pin supply voltage	$V_{CC1} - GND1$	GND1 – 0.3	18	V
Driver bias supply	$V_{CC2} - V_{EE2}$	–0.3	35	V
$V_{EE2}$ bipolar supply voltage for E version	$V_{EE2} - GND2$	–17.5	0.3	V
Output signal voltage	$V_{OUTH} - V_{EE2}, V_{OUTL} - V_{EE2}, V_{OUT} - V_{EE2}, V_{CLAMP} - V_{EE2}$	$V_{EE2} - 0.3$	$V_{CC2} + 0.3$	V
Input signal voltage	$V_{IN+} - GND1, V_{IN-} - GND1$	GND1 – 5	$V_{CC1} + 0.3$	V
Junction temperature, $T_J$ <sup>(2)</sup>		–40	150	°C
Storage temperature, $T_{stg}$		–65	150	°C

- (1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) To maintain the recommended operating conditions for  $T_J$ , see the Thermal Information table.

### 6.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS–001 <sup>(1)</sup>	V
		Charged device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 6.3 Recommended Operating Conditions

Over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
$V_{CC1}$	Supply voltage, input side	3		15	V
$V_{CC2}$	Positive supply voltage output side ( $V_{CC2} - V_{EE2}$ ), UCC53x0	13.2		33	V
$V_{CC2}$	Positive supply voltage output side ( $V_{CC2} - V_{EE2}$ ), UCC5350SBD	9.5		33	V
$V_{EE2}$	Bipolar supply voltage for E version ( $V_{EE2} - GND2$ ), UCC53x0	–16		0	V
$V_{SUP2}$	Total supply voltage output side ( $V_{CC2} - V_{EE2}$ ), UCC53x0	13.2		33	V
$T_A$	Ambient temperature	–40		125	°C

## 6.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		UCC53x0		UNIT
		D (SOIC)	DWV (SOIC)	
		8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	109.5	119.8	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	43.1	64.1	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	51.2	65.4	°C/W
$\Psi_{JT}$	Junction-to-top characterization parameter	18.3	37.6	°C/W
$\Psi_{JB}$	Junction-to-board characterization parameter	50.7	63.7	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics Application Report](#).

## 6.5 Power Ratings

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>D Package</b>						
$P_D$	Maximum power dissipation on input and output	$V_{CC1} = 15\text{ V}$ , $V_{CC2} = 15\text{ V}$ , $f = 2.1\text{-MHz}$ , 50% duty cycle, square wave, 2.2-nF load			1.14	W
$P_{D1}$	Maximum input power dissipation				0.05	W
$P_{D2}$	Maximum output power dissipation				1.09	W
<b>DWV Package</b>						
$P_D$	Maximum power dissipation on input and output	$V_{CC1} = 15\text{ V}$ , $V_{CC2} = 15\text{ V}$ , $f = 1.9\text{-MHz}$ , 50% duty cycle, square wave, 2.2-nF load			1.04	W
$P_{D1}$	Maximum input power dissipation				0.05	W
$P_{D2}$	Maximum output power dissipation				0.99	W

## 6.6 Insulation Specifications for D Package

PARAMETER		TEST CONDITIONS	VALUE	UNIT
			D	
CLR	External Clearance <sup>(1)</sup>	Shortest pin-to-pin distance through air	≥ 4	mm
CPG	External Creepage <sup>(1)</sup>	Shortest pin-to-pin distance across the package surface	≥ 4	mm
DTI	Distance through the insulation	Minimum internal gap (internal clearance)	> 21	μm
CTI	Comparative tracking index	DIN EN 60112 (VDE 0303–11); IEC 60112	> 400	V
	Material Group	According to IEC 60664–1	II	
Overvoltage category per IEC 60664-1		Rated mains voltage ≤ 150 <sub>V</sub> RMS	I-IV	
		Rated mains voltage ≤ 300 <sub>V</sub> RMS	I-III	
<b>DIN V VDE 0884–11: 2017–01<sup>(2)</sup></b>				
V <sub>IORM</sub>	Maximum repetitive peak isolation voltage	AC voltage (bipolar)	990 <sup>(6)</sup>	V <sub>PK</sub>
V <sub>IOWM</sub>	Maximum isolation working voltage	AC voltage (sine wave); time dependent dielectric breakdown (TDDb) test	700 <sup>(6)</sup>	V <sub>RMS</sub>
		DC Voltage	990 <sup>(6)</sup>	V <sub>DC</sub>
V <sub>IOTM</sub>	Maximum transient isolation voltage	V <sub>TEST</sub> = V <sub>IOTM</sub> , t = 60 s (qualification); V <sub>TEST</sub> = 1.2 × V <sub>IOTM</sub> , t = 1 s (100% production)	4242	V <sub>PK</sub>
V <sub>IOSM</sub>	Maximum surge isolation voltage <sup>(3)</sup>	Test method per IEC 62368-1, 1.2/50-μs waveform, V <sub>TEST</sub> = 1.3 × V <sub>IOSM</sub> (qualification)	4242	V <sub>PK</sub>
q <sub>pd</sub>	Apparent charge <sup>(4)</sup>	Method a: After I/O safety test subgroup 2/3, V <sub>ini</sub> = V <sub>IOTM</sub> , t <sub>ini</sub> = 60 s V <sub>pd(m)</sub> = 1.2 × V <sub>IORM</sub> , t <sub>m</sub> = 10 s	≤ 5	pC
		Method a: After environmental tests subgroup 1, V <sub>ini</sub> = V <sub>IOTM</sub> , t <sub>ini</sub> = 60 s; V <sub>pd(m)</sub> = 1.2 × V <sub>IORM</sub> , t <sub>m</sub> = 10 s	≤ 5	
		Method b1: At routine test (100% production) and preconditioning (type test), V <sub>ini</sub> = 1.2 × V <sub>IOTM</sub> , t <sub>ini</sub> = 1 s; V <sub>pd(m)</sub> = 1.5 × V <sub>IORM</sub> , t <sub>m</sub> = 1 s	≤ 5	
C <sub>IO</sub>	Barrier capacitance, input to output <sup>(5)</sup>	V <sub>IO</sub> = 0.4 × sin(2πft), f = 1 MHz	1.2	pF
R <sub>IO</sub>	Isolation resistance, input to output <sup>(5)</sup>	V <sub>IO</sub> = 500 V, T <sub>A</sub> = 25°C	> 10 <sup>12</sup>	Ω
		V <sub>IO</sub> = 500 V, 100°C ≤ T <sub>A</sub> ≤ 125°C	> 10 <sup>11</sup>	
		V <sub>IO</sub> = 500 V at T <sub>S</sub> = 150°C	> 10 <sup>9</sup>	
	Pollution degree		2	
	Climatic category		40/125/21	
<b>UL 1577</b>				
V <sub>ISO</sub>	Withstand isolation voltage	V <sub>TEST</sub> = V <sub>ISO</sub> , t = 60 s (qualification); V <sub>TEST</sub> = 1.2 × V <sub>ISO</sub> , t = 1 s (100% production)	3000	V <sub>RMS</sub>

- (1) Creepage and clearance requirements should be applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed-circuit board do not reduce this distance. Creepage and clearance on a printed-circuit board become equal in certain cases. Techniques such as inserting grooves, ribs, or both on a printed circuit board are used to help increase these specifications.
- (2) This coupler is suitable for basic electrical insulation only within the maximum operating ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.
- (3) Testing is carried out in air or oil to determine the intrinsic surge immunity of the isolation barrier.
- (4) Apparent charge is electrical discharge caused by a partial discharge (pd).
- (5) All pins on each side of the barrier tied together creating a two-pin device.
- (6) System isolation working voltages need to be verified according to application parameters.



## 6.7 Insulation Specifications for DWV Package

PARAMETER		TEST CONDITIONS	VALUE	UNIT
			DWV	
CLR	External Clearance <sup>(1)</sup>	Shortest pin-to-pin distance through air	≥ 8.5	mm
CPG	External Creepage <sup>(1)</sup>	Shortest pin-to-pin distance across the package surface	≥ 8.5	mm
DTI	Distance through the insulation	Minimum internal gap (internal clearance)	> 21	μm
CTI	Comparative tracking index	DIN EN 60112 (VDE 0303-11); IEC 60112	> 600	V
	Material Group	According to IEC 60664-1	I	
Overvoltage category per IEC 60664-1		Rated mains voltage ≤ 600 <sub>V</sub> RMS	I-III	
		Rated mains voltage ≤ 1000 <sub>V</sub> RMS	I-II	
<b>DIN V VDE 0884-11: 2017-01<sup>(2)</sup></b>				
V <sub>IORM</sub>	Maximum repetitive peak isolation voltage	AC voltage (bipolar)	2121	V <sub>PK</sub>
V <sub>IOWM</sub>	Maximum isolation working voltage	AC voltage (sine wave); time dependent dielectric breakdown (TDDb) test	1500	V <sub>RMS</sub>
		DC Voltage	2121	V <sub>DC</sub>
V <sub>IOTM</sub>	Maximum transient isolation voltage	V <sub>TEST</sub> = V <sub>IOTM</sub> , t = 60 s (qualification) ; V <sub>TEST</sub> = 1.2 × V <sub>IOTM</sub> , t = 1 s (100% production)	7000	V <sub>PK</sub>
V <sub>IOSM</sub>	Maximum surge isolation voltage <sup>(3)</sup>	Test method per IEC 62368-1, 1.2/50-μs waveform, V <sub>TEST</sub> = 1.6 × V <sub>IOSM</sub> (qualification)	8000	V <sub>PK</sub>
q <sub>pd</sub>	Apparent charge <sup>(4)</sup>	Method a: After I/O safety test subgroup 2/3, V <sub>ini</sub> = V <sub>IOTM</sub> , t <sub>ini</sub> = 60 s V <sub>pd(m)</sub> = 1.2 × V <sub>IORM</sub> , t <sub>m</sub> = 10 s	≤ 5	pC
		Method a: After environmental tests subgroup 1, V <sub>ini</sub> = V <sub>IOTM</sub> , t <sub>ini</sub> = 60 s; V <sub>pd(m)</sub> = 1.6 × V <sub>IORM</sub> , t <sub>m</sub> = 10 s	≤ 5	
		Method b1: At routine test (100% production) and preconditioning (type test), V <sub>ini</sub> = 1.2 × V <sub>IOTM</sub> , t <sub>ini</sub> = 1 s; V <sub>pd(m)</sub> = 1.875 × V <sub>IORM</sub> , t <sub>m</sub> = 1 s	≤ 5	
C <sub>IO</sub>	Barrier capacitance, input to output <sup>(5)</sup>	V <sub>IO</sub> = 0.4 × sin(2πft), f = 1 MHz	1.2	pF
R <sub>IO</sub>	Isolation resistance, input to output <sup>(5)</sup>	V <sub>IO</sub> = 500 V, T <sub>A</sub> = 25°C	> 10 <sup>12</sup>	Ω
		V <sub>IO</sub> = 500 V, 100°C ≤ T <sub>A</sub> ≤ 125°C	> 10 <sup>11</sup>	
		V <sub>IO</sub> = 500 V at T <sub>S</sub> = 150°C	> 10 <sup>9</sup>	
	Pollution degree		2	
	Climatic category		40/125/21	
<b>UL 1577</b>				
V <sub>ISO</sub>	Withstand isolation voltage	V <sub>TEST</sub> = V <sub>ISO</sub> , t = 60 s (qualification); V <sub>TEST</sub> = 1.2 × V <sub>ISO</sub> , t = 1 s (100% production)	5000	V <sub>RMS</sub>

- (1) Creepage and clearance requirements should be applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed-circuit board do not reduce this distance. Creepage and clearance on a printed-circuit board become equal in certain cases. Techniques such as inserting grooves, ribs, or both on a printed circuit board are used to help increase these specifications.
- (2) This coupler is suitable for safe electrical insulation only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.
- (3) Testing is carried out in air or oil to determine the intrinsic surge immunity of the isolation barrier.
- (4) Apparent charge is electrical discharge caused by a partial discharge (pd).
- (5) All pins on each side of the barrier tied together creating a two-pin device.

## 6.8 Safety-Related Certifications For D Package

VDE	UL	CQC
Certified according to DIN V VDE V 0884–11:2017–01 and DIN EN 61010-1 (VDE 0411-1):2011-07	Recognized under UL 1577 Component Recognition Program	Certified according to GB 4943.1–2011
Basic Insulation Maximum Transient Isolation Overvoltage, 4242 V <sub>PK</sub> ; Maximum Repetitive Peak Voltage, 990 V <sub>PK</sub> ; Maximum Surge Isolation Voltage, 4242 V <sub>PK</sub>	Single protection, 3000 V <sub>RMS</sub>	Basic Insulation, Altitude ≤ 5000m, Tropical Climate, 700 V <sub>RMS</sub> Maximum Working Voltage
Certificate Number: 40047657	File Number: E181974	Certification number: CQC18001199354

## 6.9 Safety-Related Certifications For DWV Package

VDE	UL	CQC
Plan to certify according to DIN V VDE V 0884–11:2017–01 and DIN EN 61010-1	Recognized under UL 1577 Component Recognition Program	Plan to certify according to GB 4943.1–2011
Reinforced Insulation Maximum Transient Isolation Overvoltage, 7000 V <sub>PK</sub> ; Maximum Repetitive Peak Isolation Voltage, 2121 V <sub>PK</sub> ; Maximum Surge Isolation Voltage, 8000 V <sub>PK</sub>	Single protection, 5000 V <sub>RMS</sub>	Reinforced Insulation, Altitude ≤ 5000 m, Tropical Climate
Certification number: 40047657	File Number: E181974	Certification planned

## 6.10 Safety Limiting Values

Safety limiting intends to minimize potential damage to the isolation barrier upon failure of input or output circuitry.

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
<b>D PACKAGE</b>							
I <sub>S</sub>	Safety output supply current	R <sub>θJA</sub> = 109.5°C/W, V <sub>CC2</sub> = 15 V, T <sub>J</sub> = 150°C, T <sub>A</sub> = 25°C, see <a href="#">6-1</a>	Output side			73	mA
		R <sub>θJA</sub> = 109.5°C/W, V <sub>CC2</sub> = 30 V, T <sub>J</sub> = 150°C, T <sub>A</sub> = 25°C, see <a href="#">6-1</a>	Output side			36	
P <sub>S</sub>	Safety output supply power	R <sub>θJA</sub> = 109.5°C/W, T <sub>J</sub> = 150°C, T <sub>A</sub> = 25°C, see <a href="#">6-3</a>	Input side			0.05	W
			Output side			1.09	
			Total			1.14	
T <sub>S</sub>	Maximum safety temperature <sup>(1)</sup>					150	°C
<b>DWV PACKAGE</b>							
I <sub>S</sub>	Safety input, output, or supply current	R <sub>θJA</sub> = 119.8°C/W, V <sub>I</sub> = 15 V, T <sub>J</sub> = 150°C, T <sub>A</sub> = 25°C, see <a href="#">6-2</a>	Output side			66	mA
		R <sub>θJA</sub> = 119.8°C/W, V <sub>I</sub> = 30 V, T <sub>J</sub> = 150°C, T <sub>A</sub> = 25°C, see <a href="#">6-2</a>	Output side			33	
P <sub>S</sub>	Safety input, output, or total power	R <sub>θJA</sub> = 119.8°C/W, T <sub>J</sub> = 150°C, T <sub>A</sub> = 25°C, see <a href="#">6-4</a>	Input side			0.05	W
			Output side			0.99	
			Total			1.04	
T <sub>S</sub>	Maximum safety temperature <sup>(1)</sup>					150	°C

- (1) The maximum safety temperature, T<sub>S</sub>, has the same value as the maximum junction temperature, T<sub>J</sub>, specified for the device. The I<sub>S</sub> and P<sub>S</sub> parameters represent the safety current and safety power respectively. The maximum limits of I<sub>S</sub> and P<sub>S</sub> should not be exceeded. These limits vary with the ambient temperature, T<sub>A</sub>.

The junction-to-air thermal resistance, R<sub>θJA</sub>, in the Thermal Information table is that of a device installed on a high-K test board for leaded surface-mount packages. Use these equations to calculate the value for each parameter:

$$T_J = T_A + R_{\theta JA} \times P, \text{ where } P \text{ is the power dissipated in the device.}$$

$$T_{J(max)} = T_S = T_A + R_{\theta JA} \times P_S, \text{ where } T_{J(max)} \text{ is the maximum allowed junction temperature.}$$

$$P_S = I_S \times V_I, \text{ where } V_I \text{ is the maximum input voltage.}$$

## 6.11 Electrical Characteristics

$V_{CC1} = 3.3\text{ V}$  or  $5\text{ V}$ ,  $0.1\text{-}\mu\text{F}$  capacitor from  $V_{CC1}$  to GND1,  $V_{CC2} = 15\text{ V}$ ,  $1\text{-}\mu\text{F}$  capacitor from  $V_{CC2}$  to  $V_{EE2}$ ,  $C_L = 100\text{-pF}$ ,  $T_A = -40^\circ\text{C}$  to  $+125^\circ\text{C}$ , (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>SUPPLY CURRENTS</b>						
$I_{VCC1}$	Input supply quiescent current			1.67	2.4	mA
$I_{VCC2}$	Output supply quiescent current			1.1	1.8	mA
<b>SUPPLY VOLTAGE UNDERVOLTAGE THRESHOLDS</b>						
$V_{IT+}(UVLO1)$	VCC1 Positive-going UVLO threshold voltage			2.6	2.8	V
$V_{IT-}(UVLO1)$	VCC1 Negative-going UVLO threshold voltage		2.4	2.5		V
$V_{hys}(UVLO1)$	VCC1 UVLO threshold hysteresis			0.1		V
<b>UCC5310MC, UCC5320SC, UCC5320EC, UCC5390SC, UCC5390EC, and UCC5350MC UVLO THRESHOLDS (12-V UVLO Version)</b>						
$V_{IT+}(UVLO2)$	VCC2 Positive-going UVLO threshold voltage			12	13	V
$V_{IT-}(UVLO2)$	VCC2 Negative-going UVLO threshold voltage		10.3	11		V
$V_{hys}(UVLO2)$	VCC2 UVLO threshold voltage hysteresis			1		V
<b>UCC5350SB UVLO THRESHOLD (8-V UVLO Version)</b>						
$V_{IT+}(UVLO2)$	VCC2 Positive-going UVLO threshold voltage			8.7	9.4	V
$V_{IT-}(UVLO2)$	VCC2 Negative-going UVLO threshold voltage		7.3	8.0		V
$V_{hys}(UVLO2)$	VCC2 UVLO threshold voltage hysteresis			0.7		V
<b>LOGIC I/O</b>						
$V_{IT+}(IN)$	Positive-going input threshold voltage (IN+, IN-)			$0.55 \times V_{CC1}$	$0.7 \times V_{CC1}$	V
$V_{IT-}(IN)$	Negative-going input threshold voltage (IN+, IN-)		$0.3 \times V_{CC1}$	$0.45 \times V_{CC1}$		V
$V_{hys}(IN)$	Input hysteresis voltage (IN+, IN-)			$0.1 \times V_{CC1}$		V
$I_{IH}$	High-level input leakage at IN+	IN+ = $V_{CC1}$		40	240	$\mu\text{A}$
$I_{IL}$	Low-level input leakage at IN-	IN- = GND1	-240	-40		$\mu\text{A}$
		IN- = GND1 - 5 V	-310	-80		
<b>GATE DRIVER STAGE</b>						
$V_{OH}$	High-level output voltage (VCC2 - OUT) and (VCC2 - OUTH)	$I_{OUT} = -20\text{ mA}$	100	240		mV
$V_{OL}$	Low level output voltage (OUT and OUTL)	UCC5320SC and UCC5320EC, IN+ = low, IN- = high; $I_O = 20\text{ mA}$	9.4	13		mV
		UCC5310MC, IN+ = low, IN- = high; $I_O = 20\text{ mA}$	17	26		
		UCC5390SC and UCC5390EC, IN+ = low, IN- = high; $I_O = 20\text{ mA}$	2	3		
		UCC5350MC and UCC5350SB, IN+ = low, IN- = high; $I_O = 20\text{ mA}$	5	7		

## 6.11 Electrical Characteristics (続き)

$V_{CC1} = 3.3\text{ V}$  or  $5\text{ V}$ ,  $0.1\text{-}\mu\text{F}$  capacitor from  $V_{CC1}$  to GND1,  $V_{CC2} = 15\text{ V}$ ,  $1\text{-}\mu\text{F}$  capacitor from  $V_{CC2}$  to  $V_{EE2}$ ,  $C_L = 100\text{-pF}$ ,  $T_A = -40^\circ\text{C}$  to  $+125^\circ\text{C}$ , (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$I_{OH}$	Peak source current	UCC5320SC and UCC5320EC, IN+ = high, IN- = low	2.4	4.3		A
		UCC5310MC, IN+ = high, IN- = low	2.4	4.3		
		UCC5390SC and UCC5390EC, IN+ = high, IN- = low	10	17		
		UCC5350MC, IN+ = high, IN- = low	5	10		
		UCC5350SB IN+ = high, IN- = low	5	8.5		
$I_{OL}$	Peak sink current	UCC5320SC and UCC5320EC, IN+ = low, IN- = high	2.2	4.4		A
		UCC5310MC, IN+ = low, IN- = high	1.1	2.2		
		UCC5390SC and UCC5390EC, IN+ = low, IN- = high	10	17		
		UCC5350MC, IN+ = low, IN- = high	5	10		
		UCC5350SB IN+ = low, IN- = high	5	10		
<b>ACTIVE MILLER CLAMP (UCC53xxM only)</b>						
$V_{CLAMP}$	Low-level clamp voltage	UCC5310MC, $I_{CLAMP} = 20\text{ mA}$		26	50	mV
		UCC5350MC, $I_{CLAMP} = 20\text{ mA}$		7	10	
$I_{CLAMP}$	Clamp low-level current	UCC5310MC, $V_{CLAMP} = V_{EE2} + 15\text{ V}$	1.1	2.2		A
		UCC5350MC, $V_{CLAMP} = V_{EE2} + 15\text{ V}$	5	10		
$I_{CLAMP(L)}$	Clamp low-level current for low output voltage	UCC5310MC, $V_{CLAMP} = V_{EE2} + 2\text{ V}$	0.7	1.5		A
		UCC5350MC, $V_{CLAMP} = V_{EE2} + 2\text{ V}$	5	10		
$V_{CLAMP-TH}$	Clamp threshold voltage	UCC5310MC and UCC5350MC		2.1	2.3	V
<b>SHORT CIRCUIT CLAMPING</b>						
$V_{CLP-OUT}$	Clamping voltage ( $V_{OUTH} - V_{CC2}$ or $V_{OUT} - V_{CC2}$ )	IN+ = high, IN- = low, $t_{CLAMP} = 10\text{ }\mu\text{s}$ , $I_{OUTH}$ or $I_{OUT} = 500\text{ mA}$		1	1.3	V
$V_{CLP-OUT}$	Clamping voltage ( $V_{EE2} - V_{OUTL}$ or $V_{EE2} - V_{CLAMP}$ or $V_{EE2} - V_{OUT}$ )	IN+ = low, IN- = high, $t_{CLAMP} = 10\text{ }\mu\text{s}$ , $I_{CLAMP}$ or $I_{OUTL} = -500\text{ mA}$		1.5		V
		IN+ = low, IN- = high, $I_{CLAMP}$ or $I_{OUTL} = -20\text{ mA}$		0.9	1	
<b>ACTIVE PULLDOWN</b>						
$V_{OUTSD}$	Active pulldown voltage on OUTL, CLAMP, OUT	$I_{OUTL}$ or $I_{OUT} = 0.1 \times I_{OUTL(typ)}$ , $V_{CC2} =$ open		1.8	2.5	V

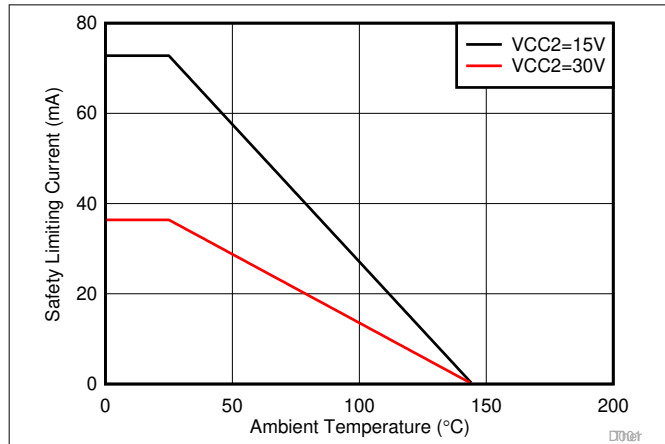
## 6.12 Switching Characteristics

$V_{CC1} = 3.3\text{ V}$  or  $5\text{ V}$ ,  $0.1\text{-}\mu\text{F}$  capacitor from  $V_{CC1}$  to GND1,  $V_{CC2} = 15\text{ V}$ ,  $1\text{-}\mu\text{F}$  capacitor from  $V_{CC2}$  to  $V_{EE2}$ ,  $T_A = -40^\circ\text{C}$  to  $+125^\circ\text{C}$ , (unless otherwise noted)

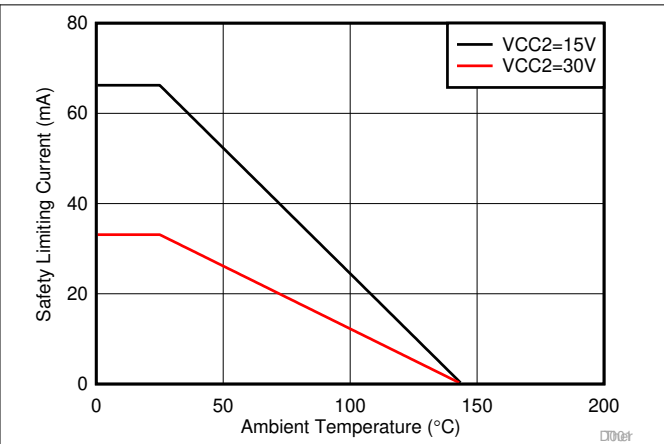
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_r$	Output-signal rise time	UCC5320SC, UCC5320EC, and UCC5310MC, $C_{LOAD} = 1\text{ nF}$		12	28	ns
		UCC5390SC, UCC5350SB, UCC5390EC, and UCC5350MC, $C_{LOAD} = 1\text{ nF}$		10	26	ns
$t_f$	Output-signal fall time	UCC5320SC and UCC5320EC, $C_{LOAD} = 1\text{ nF}$		10	25	ns
		UCC5310MC, $C_{LOAD} = 1\text{ nF}$		10	26	ns
		UCC5390SC, UCC5350SB, UCC5390EC, and UCC5350MC, $C_{LOAD} = 1\text{ nF}$		10	22	ns
$t_{PLH}$	Propagation delay (default versions), high	UCC5320SC and UCC5320EC, $C_{LOAD} = 100\text{ pF}$		60	72	ns
		UCC5310MC, $C_{LOAD} = 100\text{ pF}$		60	75	ns
		UCC5390SC, UCC5350SB, UCC5390EC, and UCC5350MC, $C_{LOAD} = 100\text{ pF}$		65	100	ns
$t_{PHL}$	Propagation delay (default versions), low	UCC5320SC and UCC5320EC, $C_{LOAD} = 100\text{ pF}$		60	75	ns
		UCC5310MC, $C_{LOAD} = 100\text{ pF}$		60	75	ns
		UCC5390SC, UCC5350SB, UCC5390EC, and UCC5350MC, $C_{LOAD} = 100\text{ pF}$		65	100	ns
$t_{UVLO1\_rec}$	UVLO recovery delay of $V_{CC1}$	See <a href="#">Figure 8-9</a>		30		$\mu\text{s}$
$t_{UVLO2\_rec}$	UVLO recovery delay of $V_{CC2}$	See <a href="#">Figure 8-9</a>		50		$\mu\text{s}$
$t_{PWD}$	Pulse width distortion $ t_{PHL} - t_{PLH} $	UCC5320SC and UCC5320EC, $C_{LOAD} = 100\text{ pF}$		1	20	ns
		UCC5310MC, $C_{LOAD} = 100\text{ pF}$		1	20	ns
		UCC5390SC, UCC5350SB, and UCC5390EC, $C_{LOAD} = 100\text{ pF}$		1	20	ns
		UCC5350MC, $C_{LOAD} = 100\text{ pF}$		1	20	ns
$t_{sk(pp)}$	Part-to-part skew <sup>(1)</sup>	UCC5320SC and UCC5320EC, $C_{LOAD} = 100\text{ pF}$		1	25	ns
		UCC5310MC, $C_{LOAD} = 100\text{ pF}$		1	25	ns
		UCC5390SC, UCC5350SB, and UCC5390EC, $C_{LOAD} = 100\text{ pF}$		1	25	ns
		UCC5350MC, $C_{LOAD} = 100\text{ pF}$		1	25	ns
CMTI	Common-mode transient immunity	PWM is tied to GND or $V_{CC1}$ , $V_{CM} = 1200\text{ V}$	100	120		$\text{kV}/\mu\text{s}$

(1)  $t_{sk(pp)}$  is the magnitude of the difference in propagation delay times between the output of different devices switching in the same direction while operating at identical supply voltages, temperature, input signals and loads guaranteed by characterization.

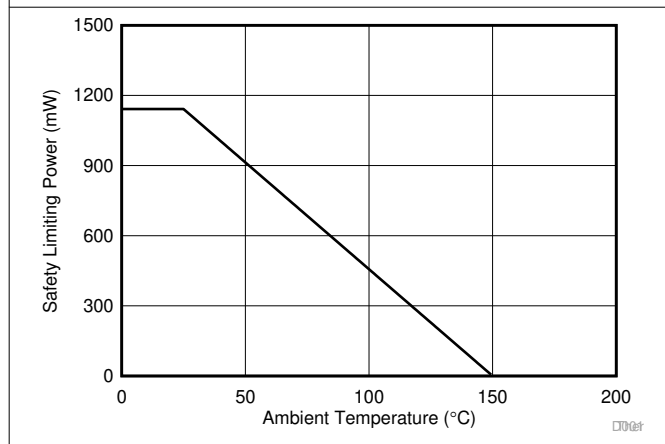
### 6.13 Insulation Characteristics Curves



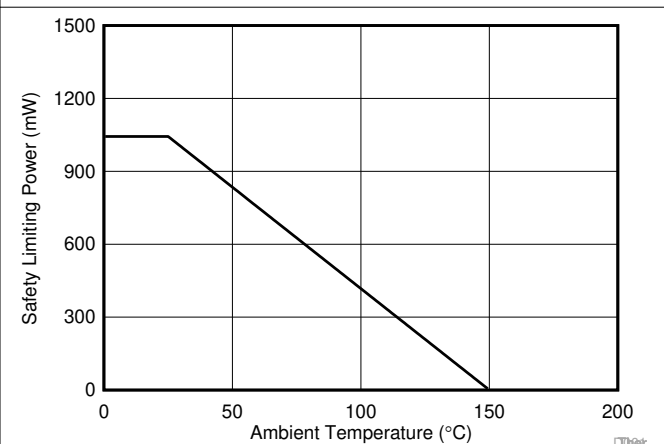
**6-1. Thermal Derating Curve for Limiting Current per VDE for D Package**



**6-2. Thermal Derating Curve for Limiting Current per VDE for DWV Package**



**6-3. Thermal Derating Curve for Limiting Power per VDE for D Package**



**6-4. Thermal Derating Curve for Limiting Power per VDE for DWV Package**

### 6.14 Typical Characteristics

$V_{CC1} = 3.3\text{ V}$  or  $5\text{ V}$ ,  $0.1\text{-}\mu\text{F}$  capacitor from  $V_{CC1}$  to  $\text{GND1}$ ,  $V_{CC2} = 15\text{ V}$ ,  $1\text{-}\mu\text{F}$  capacitor from  $V_{CC2}$  to  $V_{EE2}$ ,  $C_{LOAD} = 1\text{ nF}$ ,  $T_A = -40^\circ\text{C}$  to  $+125^\circ\text{C}$ , (unless otherwise noted)

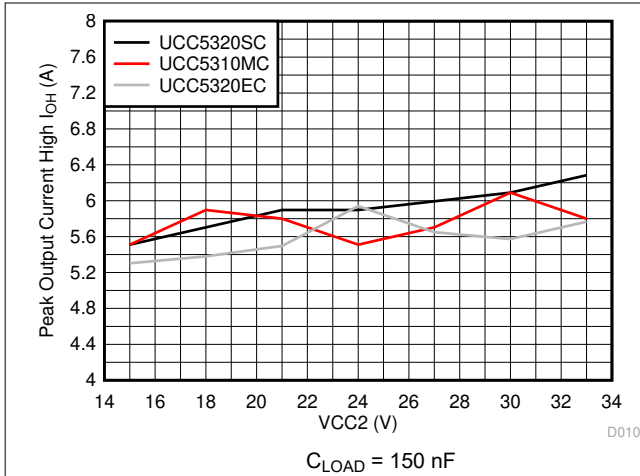


图 6-5. Output-High Drive Current vs Output Voltage

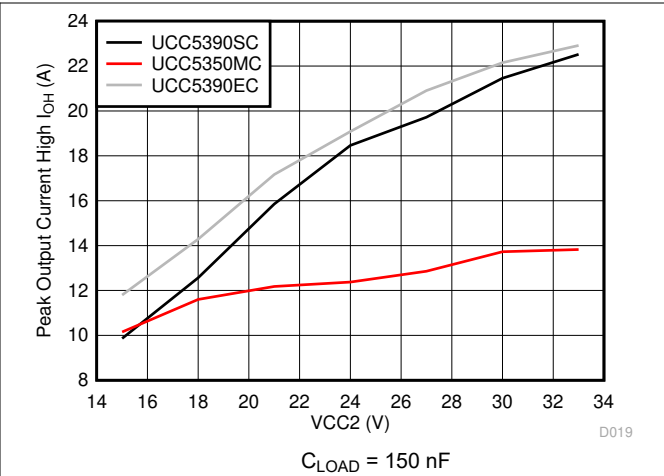


图 6-6. Output-High Drive Current vs Output Voltage

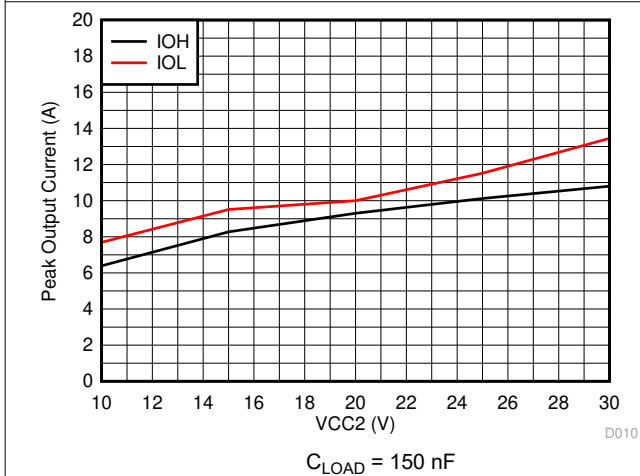


图 6-7. UCC5350SBD Output-High Drive Current vs Output Voltage

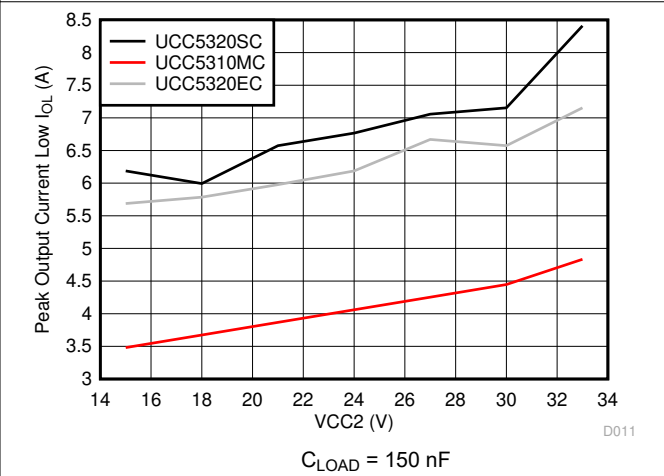


图 6-8. Output-Low Drive Current vs Output Voltage

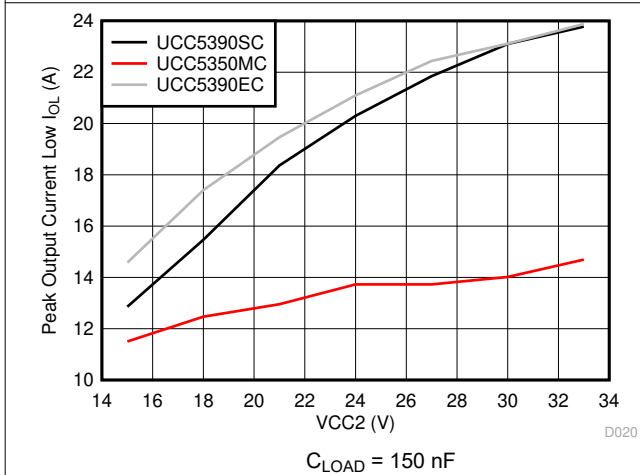


图 6-9. Output-Low Drive Current vs Output Voltage

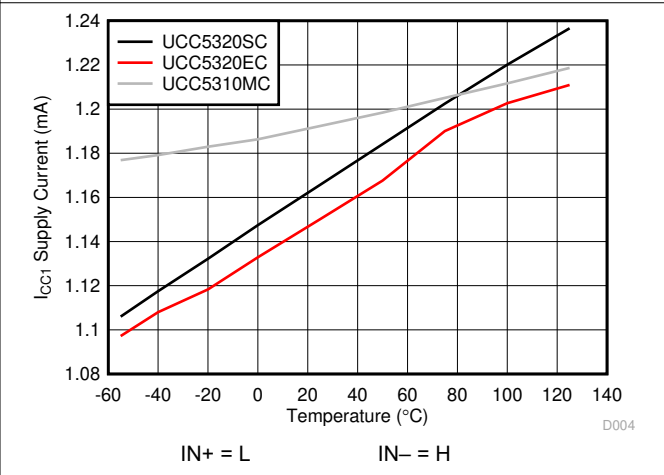
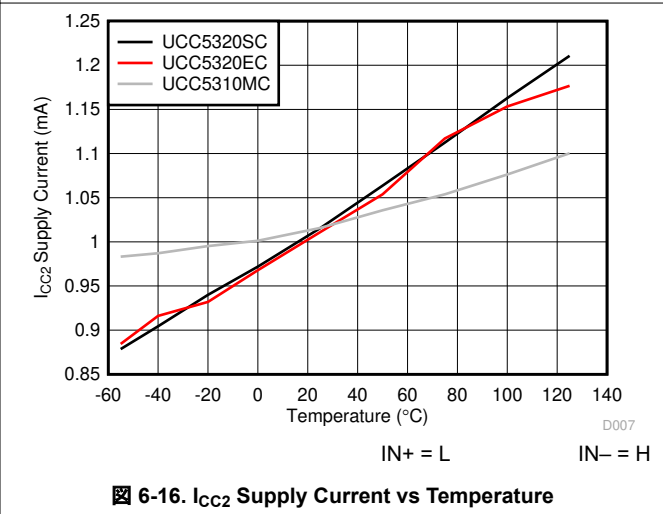
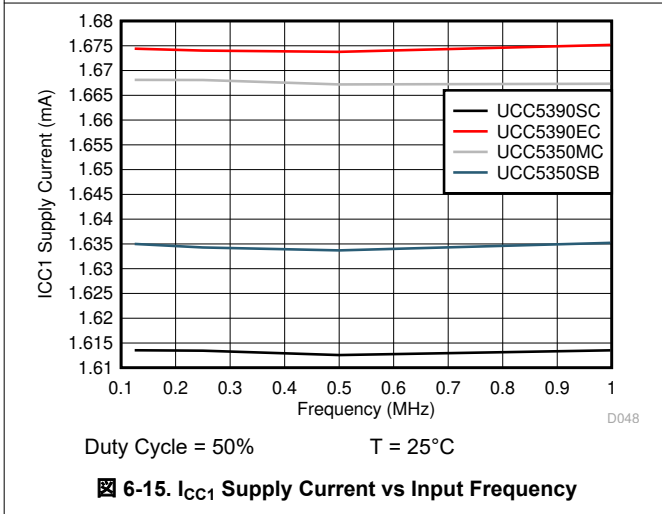
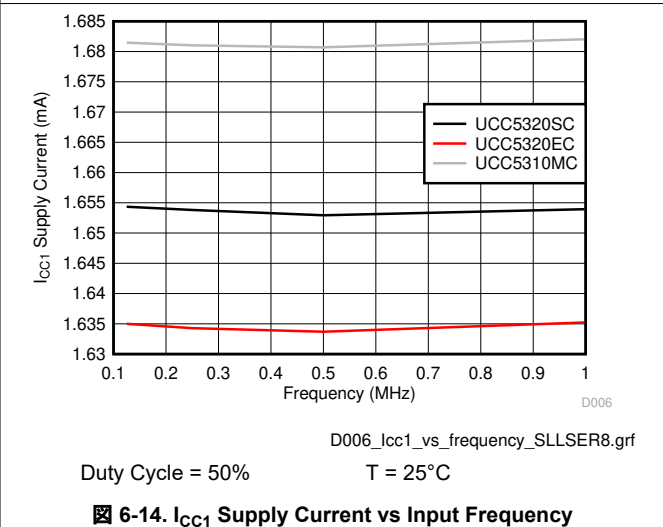
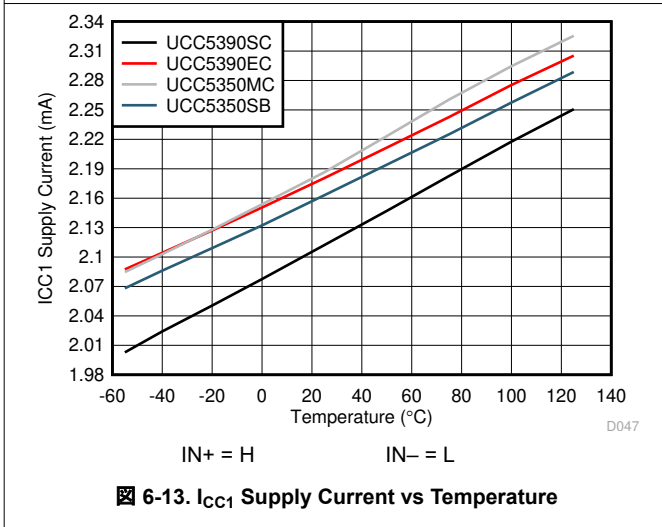
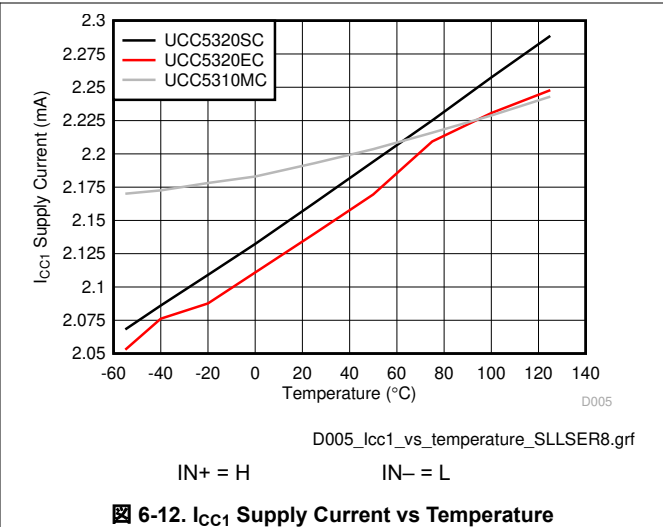
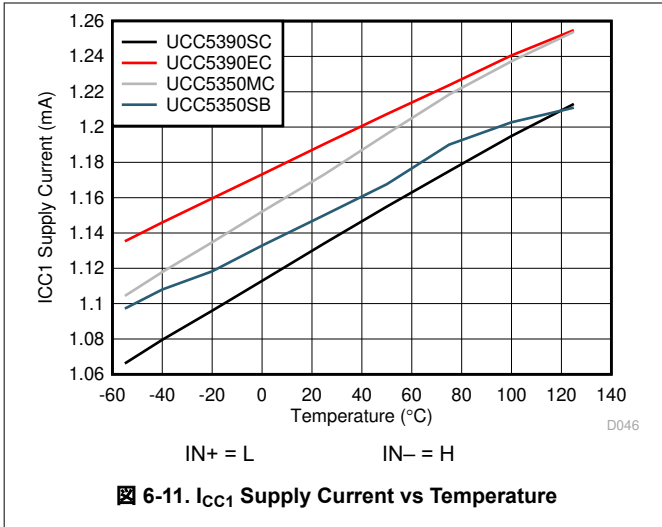


图 6-10.  $I_{CC1}$  Supply Current vs Temperature

### 6.14 Typical Characteristics (continued)

$V_{CC1} = 3.3\text{ V}$  or  $5\text{ V}$ ,  $0.1\text{-}\mu\text{F}$  capacitor from  $V_{CC1}$  to GND1,  $V_{CC2} = 15\text{ V}$ ,  $1\text{-}\mu\text{F}$  capacitor from  $V_{CC2}$  to  $V_{EE2}$ ,  $C_{LOAD} = 1\text{ nF}$ ,  $T_A = -40^\circ\text{C}$  to  $+125^\circ\text{C}$ , (unless otherwise noted)





### 6.14 Typical Characteristics (continued)

$V_{CC1} = 3.3\text{ V}$  or  $5\text{ V}$ ,  $0.1\text{-}\mu\text{F}$  capacitor from  $V_{CC1}$  to  $\text{GND1}$ ,  $V_{CC2} = 15\text{ V}$ ,  $1\text{-}\mu\text{F}$  capacitor from  $V_{CC2}$  to  $V_{EE2}$ ,  $C_{LOAD} = 1\text{ nF}$ ,  $T_A = -40^\circ\text{C}$  to  $+125^\circ\text{C}$ , (unless otherwise noted)

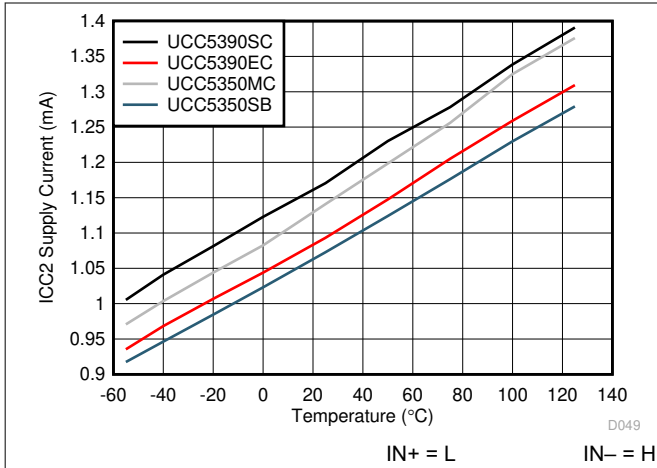


Figure 6-17.  $I_{CC2}$  Supply Current vs Temperature

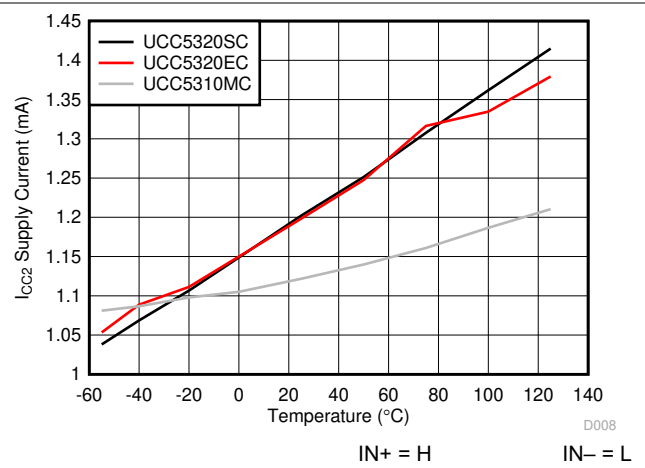


Figure 6-18.  $I_{CC2}$  Supply Current vs Temperature

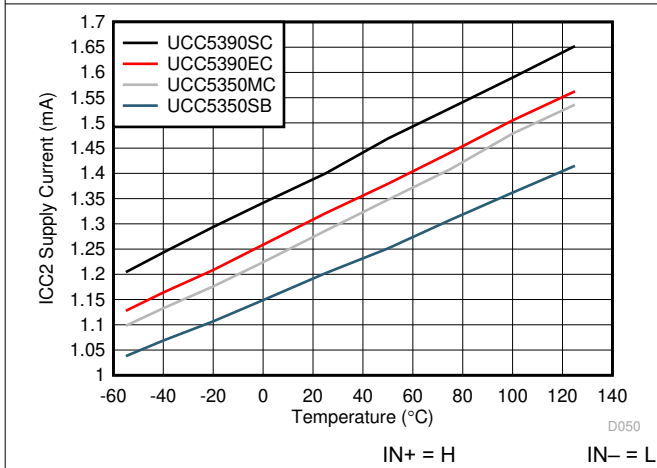


Figure 6-19.  $I_{CC2}$  Supply Current vs Temperature

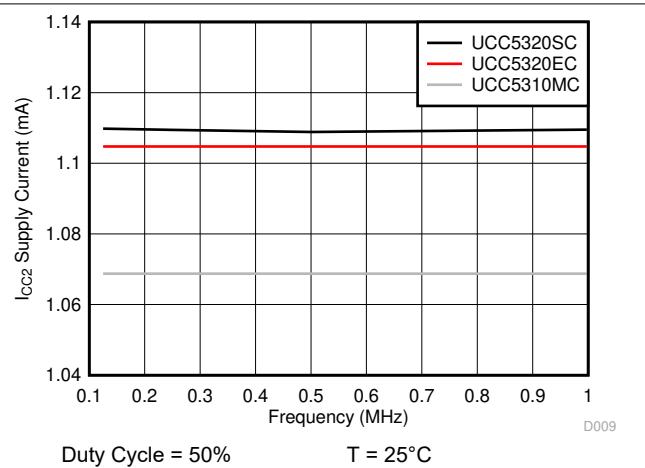


Figure 6-20.  $I_{CC2}$  Supply Current vs Input Frequency

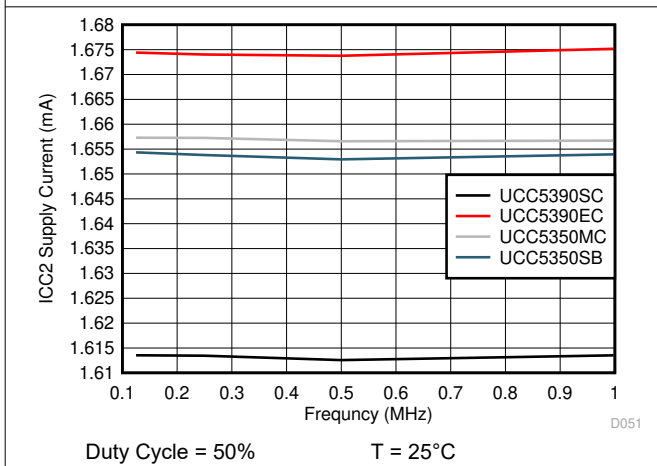


Figure 6-21.  $I_{CC2}$  Supply Current vs Input Frequency

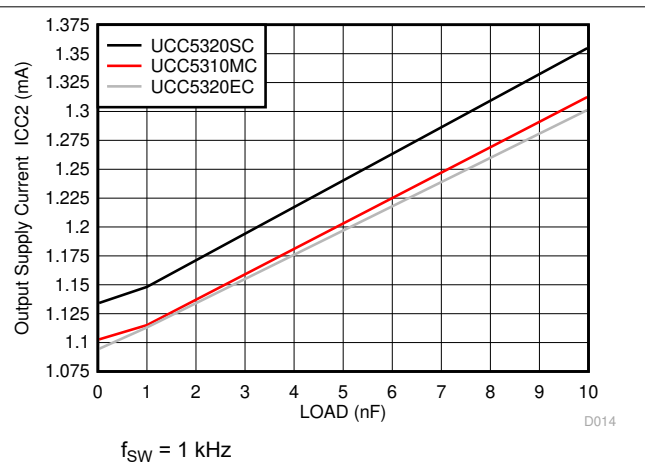
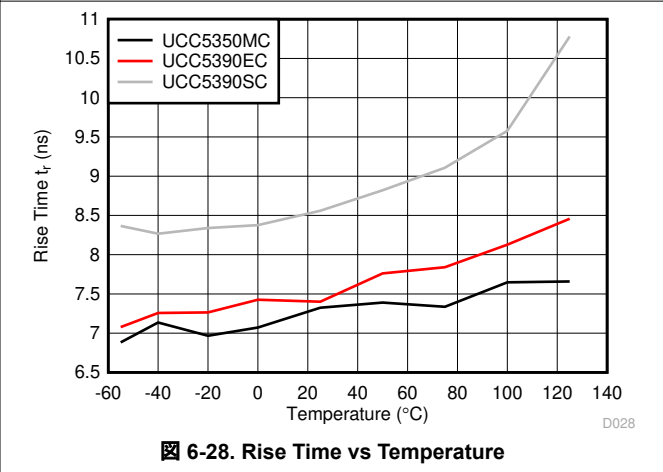
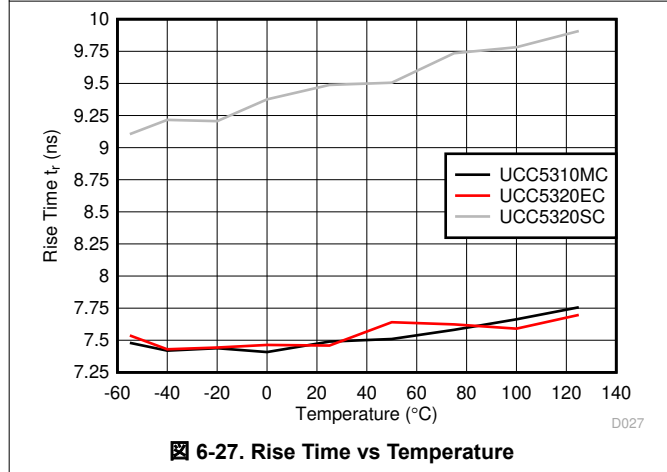
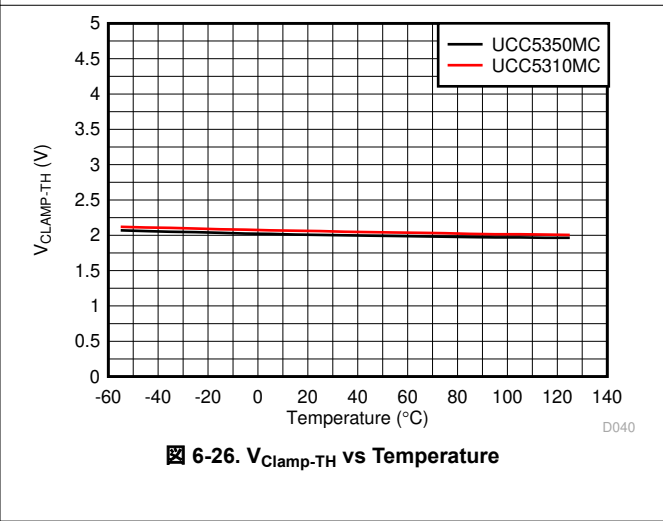
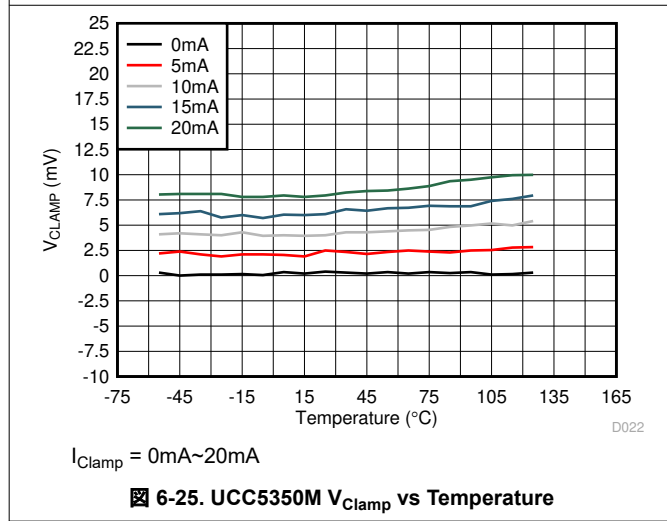
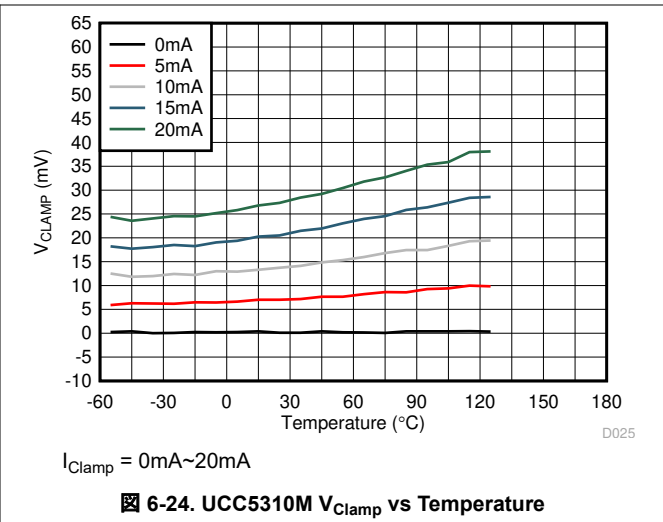
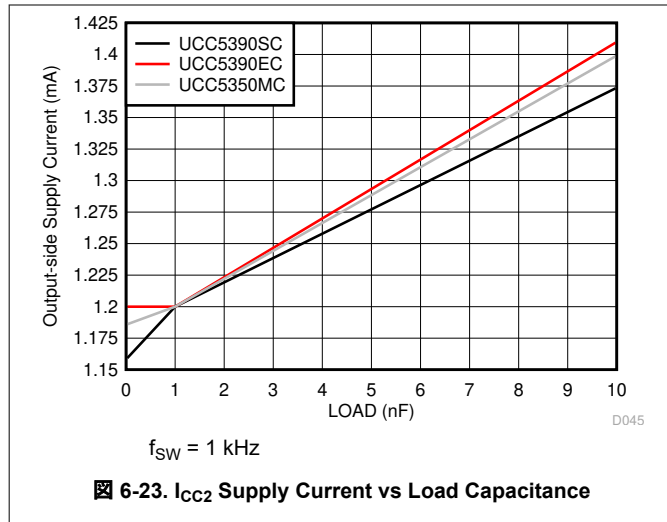


Figure 6-22.  $I_{CC2}$  Supply Current vs Load Capacitance

### 6.14 Typical Characteristics (continued)

$V_{CC1} = 3.3\text{ V}$  or  $5\text{ V}$ ,  $0.1\text{-}\mu\text{F}$  capacitor from  $V_{CC1}$  to  $\text{GND1}$ ,  $V_{CC2} = 15\text{ V}$ ,  $1\text{-}\mu\text{F}$  capacitor from  $V_{CC2}$  to  $V_{EE2}$ ,  $C_{\text{LOAD}} = 1\text{ nF}$ ,  $T_A = -40^\circ\text{C}$  to  $+125^\circ\text{C}$ , (unless otherwise noted)



### 6.14 Typical Characteristics (continued)

$V_{CC1} = 3.3\text{ V}$  or  $5\text{ V}$ ,  $0.1\text{-}\mu\text{F}$  capacitor from  $V_{CC1}$  to  $\text{GND1}$ ,  $V_{CC2} = 15\text{ V}$ ,  $1\text{-}\mu\text{F}$  capacitor from  $V_{CC2}$  to  $V_{EE2}$ ,  $C_{LOAD} = 1\text{ nF}$ ,  $T_A = -40^\circ\text{C}$  to  $+125^\circ\text{C}$ , (unless otherwise noted)

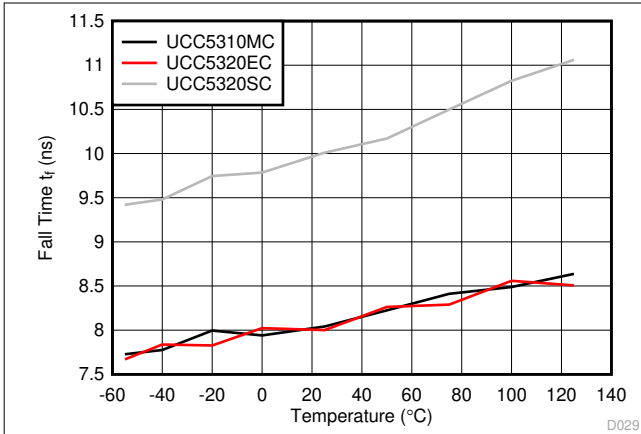


图 6-29. Fall Time Vs Temperature

D029

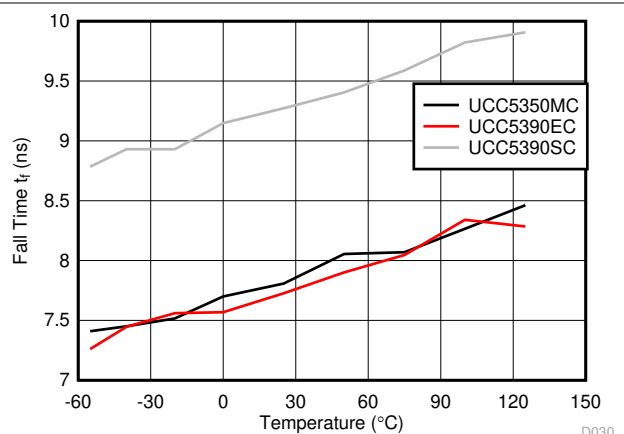


图 6-30. Fall Time vs Temperature

D030

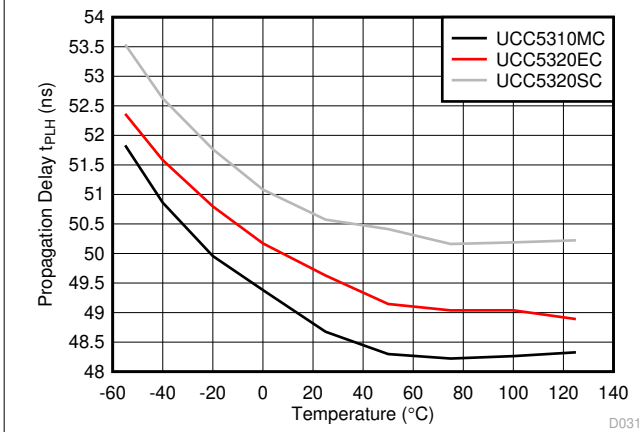


图 6-31. Propagation Delay  $t_{PLH}$  vs Temperature

D031

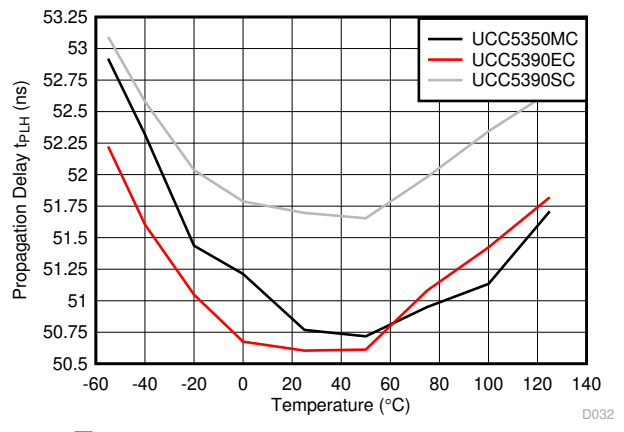


图 6-32. Propagation Delay  $t_{PLH}$  vs Temperature

D032

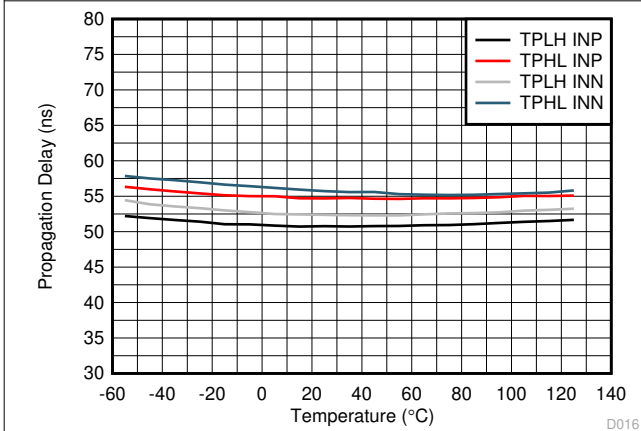


图 6-33. UCC5350SBD Propagation Delay vs Temperature

D016

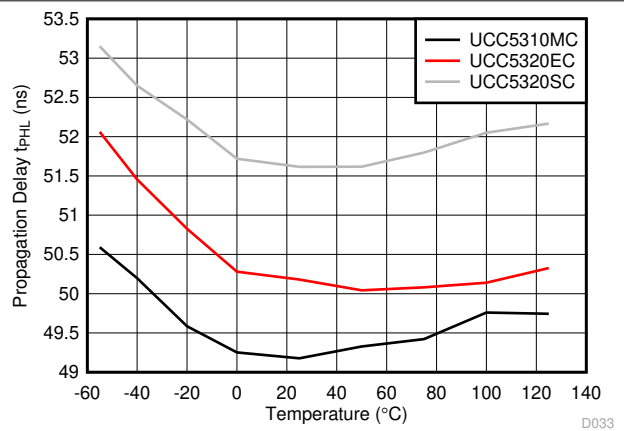
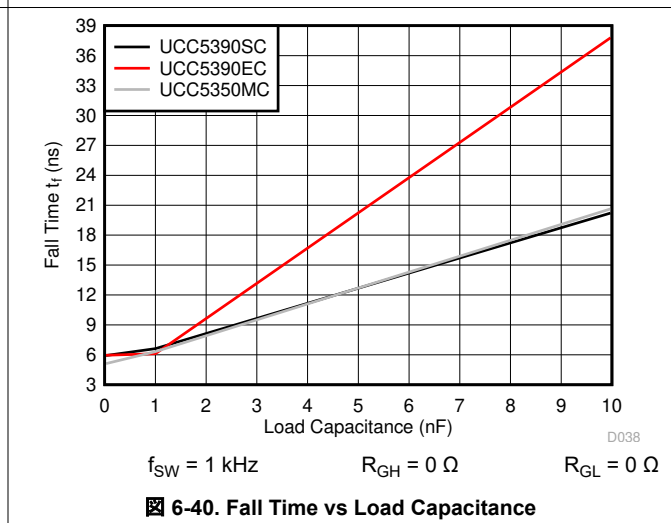
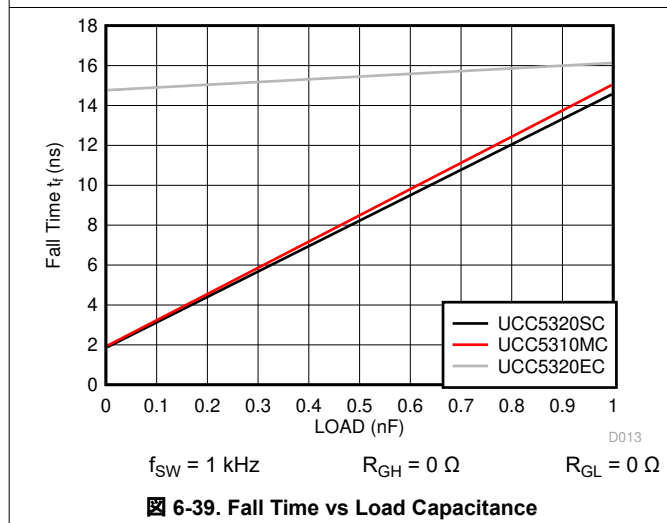
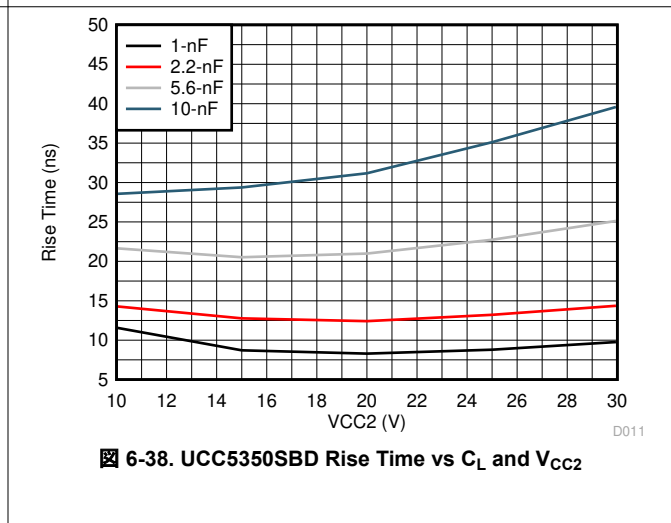
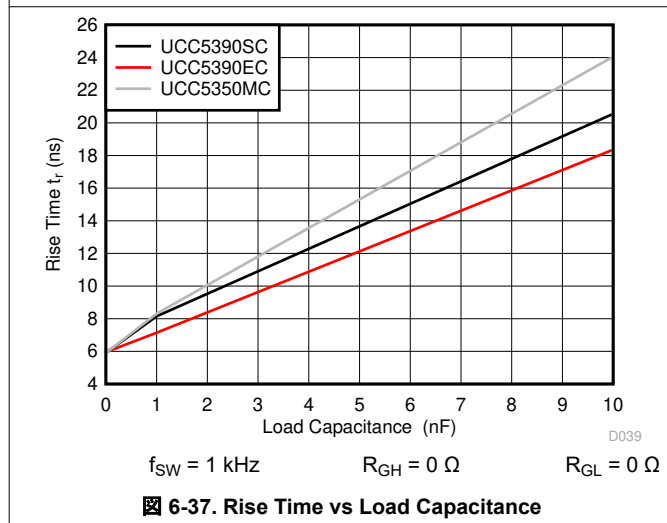
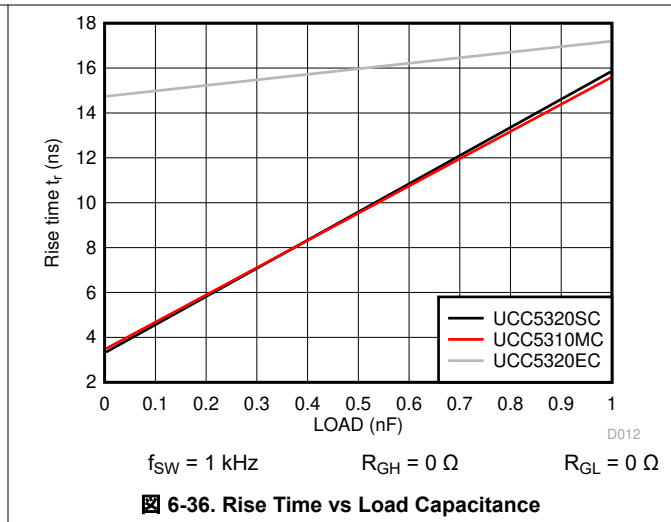
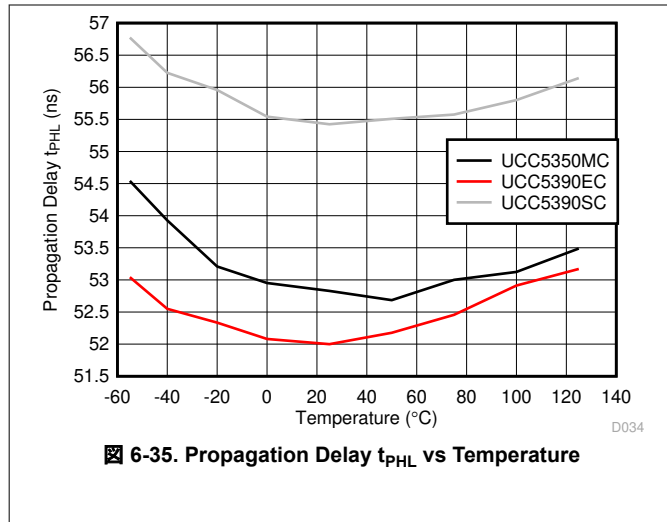


图 6-34. Propagation Delay  $t_{PHL}$  vs Temperature

D033

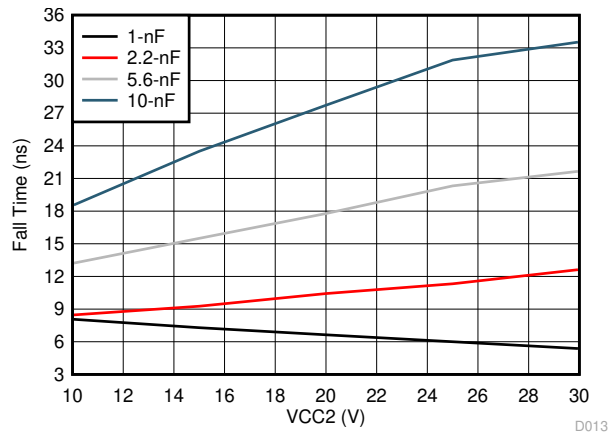
### 6.14 Typical Characteristics (continued)

$V_{CC1} = 3.3\text{ V}$  or  $5\text{ V}$ ,  $0.1\text{-}\mu\text{F}$  capacitor from  $V_{CC1}$  to  $\text{GND1}$ ,  $V_{CC2} = 15\text{ V}$ ,  $1\text{-}\mu\text{F}$  capacitor from  $V_{CC2}$  to  $V_{EE2}$ ,  $C_{\text{LOAD}} = 1\text{ nF}$ ,  $T_A = -40^\circ\text{C}$  to  $+125^\circ\text{C}$ , (unless otherwise noted)



### 6.14 Typical Characteristics (continued)

$V_{CC1} = 3.3\text{ V}$  or  $5\text{ V}$ ,  $0.1\text{-}\mu\text{F}$  capacitor from  $V_{CC1}$  to  $\text{GND1}$ ,  $V_{CC2} = 15\text{ V}$ ,  $1\text{-}\mu\text{F}$  capacitor from  $V_{CC2}$  to  $V_{EE2}$ ,  $C_{LOAD} = 1\text{ nF}$ ,  $T_A = -40^\circ\text{C}$  to  $+125^\circ\text{C}$ , (unless otherwise noted)



6-41. UCC5350SBD Fall Time vs  $C_L$  and  $V_{CC2}$

## 7 Parameter Measurement Information

### 7.1 Propagation Delay, Inverting, and Noninverting Configuration

Figure 7-1 shows the propagation delay  $t_{PLH}$  and  $t_{PHL}$  for noninverting configurations. Figure 7-2 shows the propagation delay with the inverting configuration. These figures also demonstrate the method used to measure the rise ( $t_r$ ) and fall ( $t_f$ ) times.

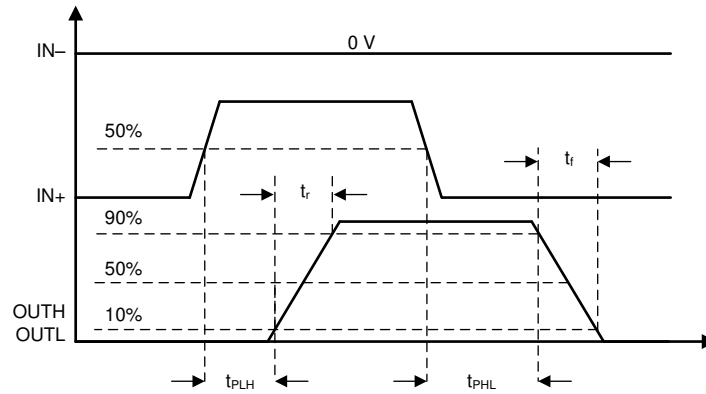


Figure 7-1.  $t_{PLH}$  and  $t_{PHL}$  Propagation Delay, Noninverting Configuration

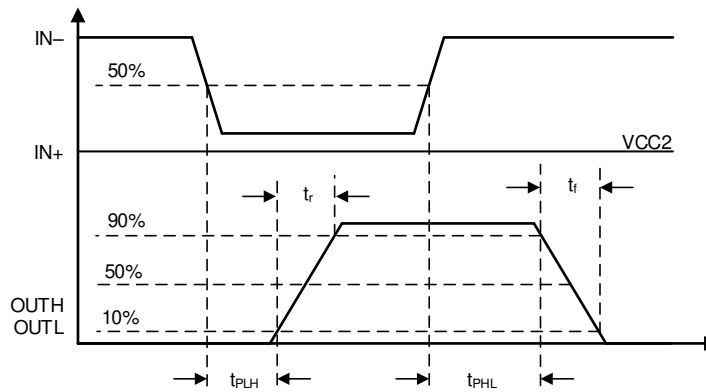
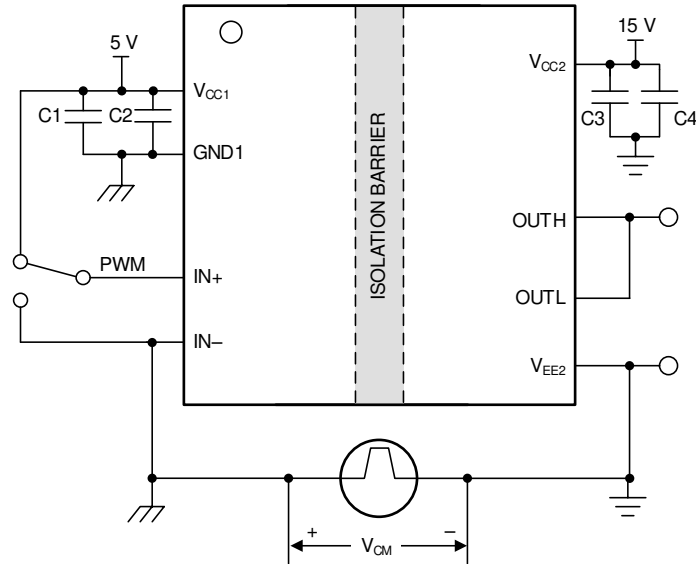


Figure 7-2.  $t_{PLH}$  and  $t_{PHL}$  Propagation Delay, Inverting Configuration

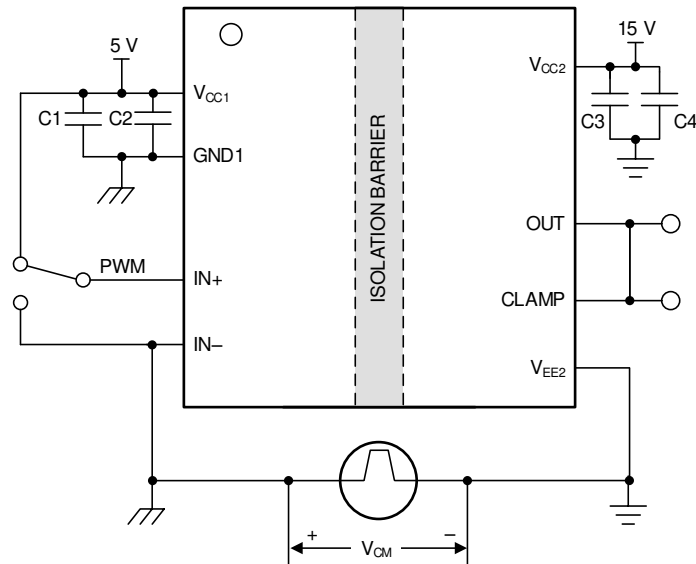
### 7.1.1 CMTI Testing

7-3, 7-4, and 7-5 are simplified diagrams of the CMTI testing configuration used for each device type.



Copyright © 2017, Texas Instruments Incorporated

7-3. CMTI Test Circuit for Split Output (UCC53x0S)



Copyright © 2017, Texas Instruments Incorporated

7-4. CMTI Test Circuit for Miller Clamp (UCC53x0M)

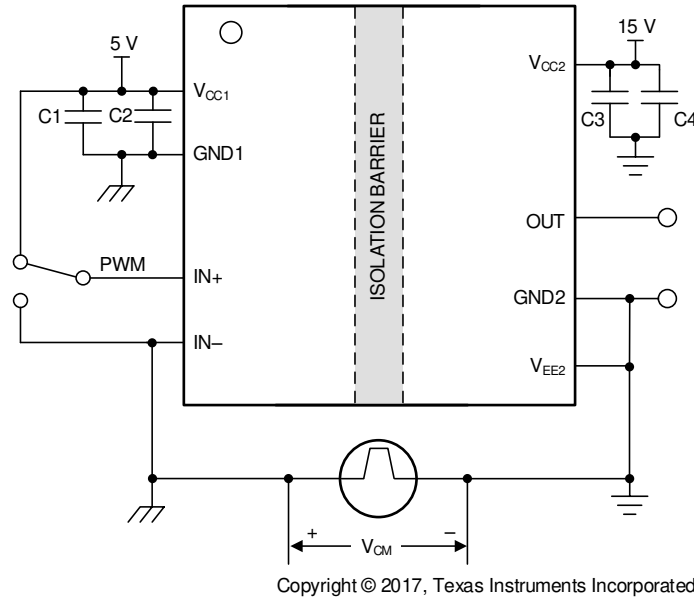


図 7-5. CMTI Test Circuit for UVLO2 with Respect to GND2 (UCC53x0E)



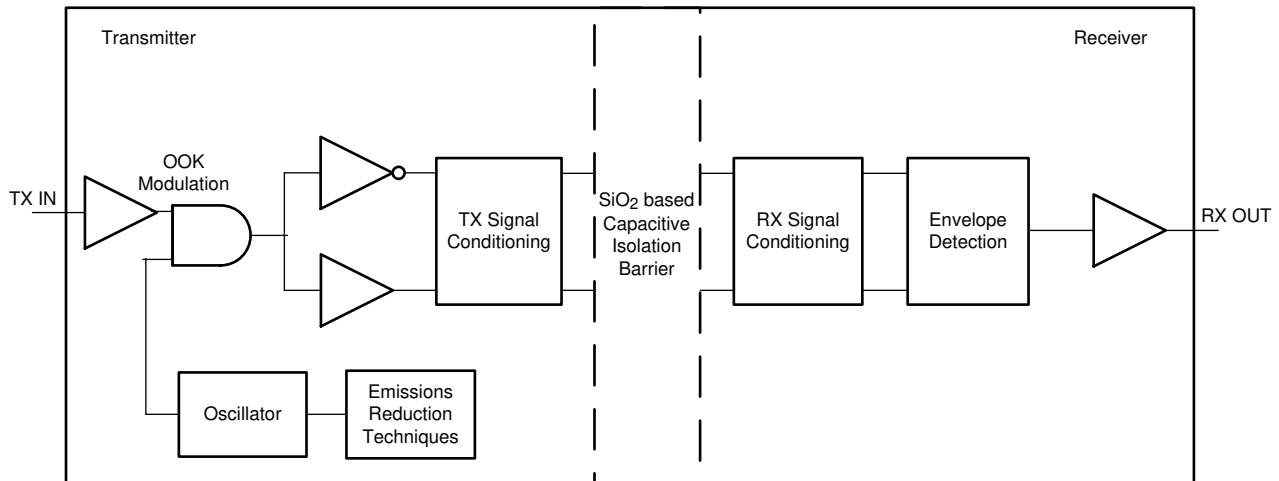
## 8 Detailed Description

### 8.1 Overview

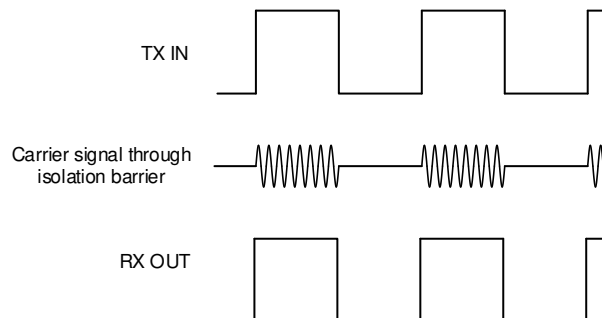
The UCC53x0 family of isolated gate drivers has three variations: split output, Miller clamp, and UVLO2 referenced to GND2 (see [セクション 4](#)). The isolation inside the UCC53x0 family of devices is implemented with high-voltage SiO<sub>2</sub>-based capacitors. The signal across the isolation has an on-off keying (OOK) modulation scheme to transmit the digital data across a silicon dioxide based isolation barrier (see [図 8-2](#)). The transmitter sends a high-frequency carrier across the barrier to represent one digital state and sends no signal to represent the other digital state. The receiver demodulates the signal after advanced signal conditioning and produces the output through a buffer stage. The UCC53x0 devices also incorporate advanced circuit techniques to maximize the CMTI performance and minimize the radiated emissions from the high frequency carrier and IO buffer switching. The conceptual block diagram of a digital capacitive isolator, [図 8-1](#), shows a functional block diagram of a typical channel. [図 8-2](#) shows a conceptual detail of how the OOK scheme works.

[図 8-1](#) shows how the input signal passes through the capacitive isolation barrier through modulation (OOK) and signal conditioning.

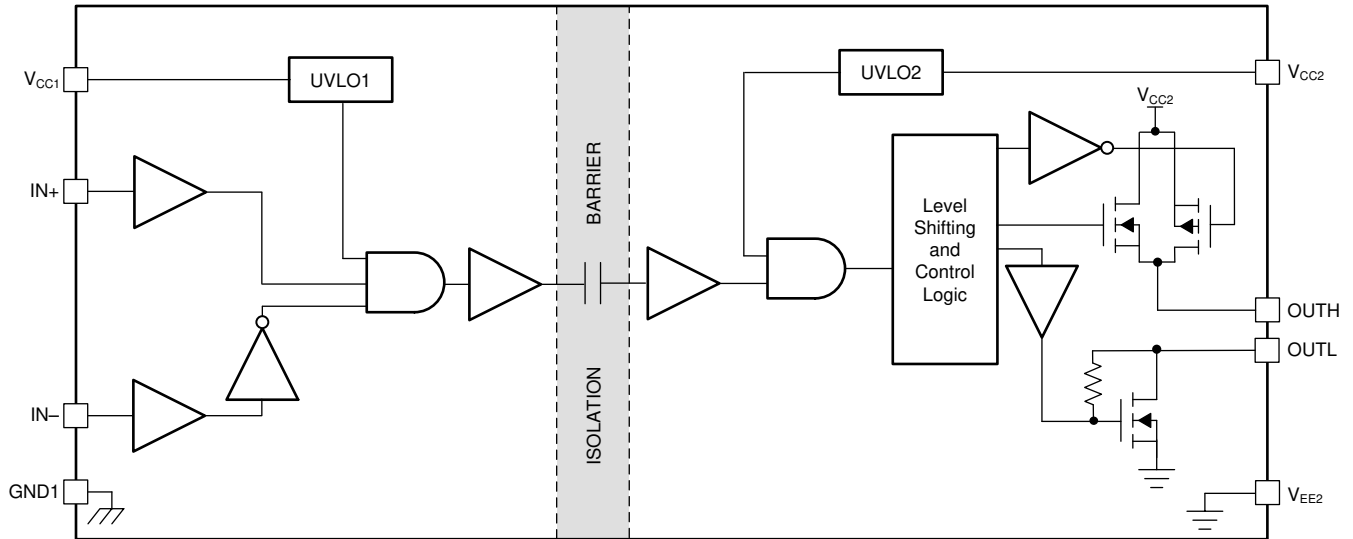
### 8.2 Functional Block Diagram



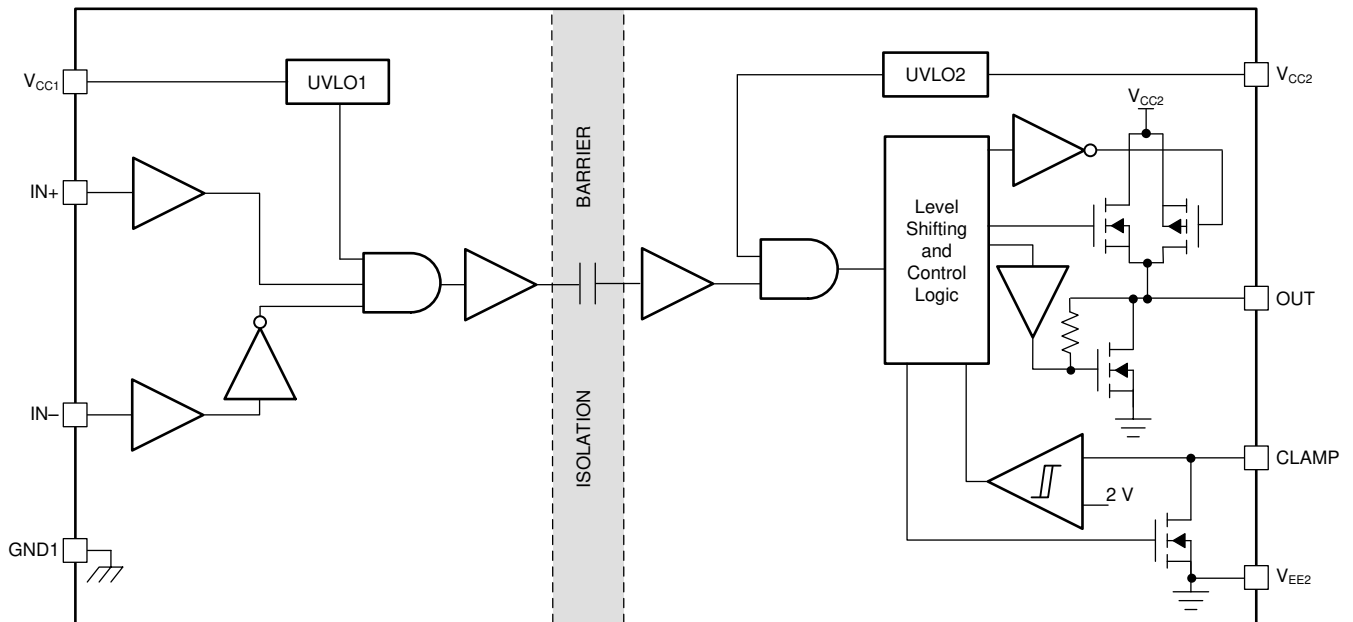
**図 8-1. Conceptual Block Diagram of a Capacitive Data Channel**



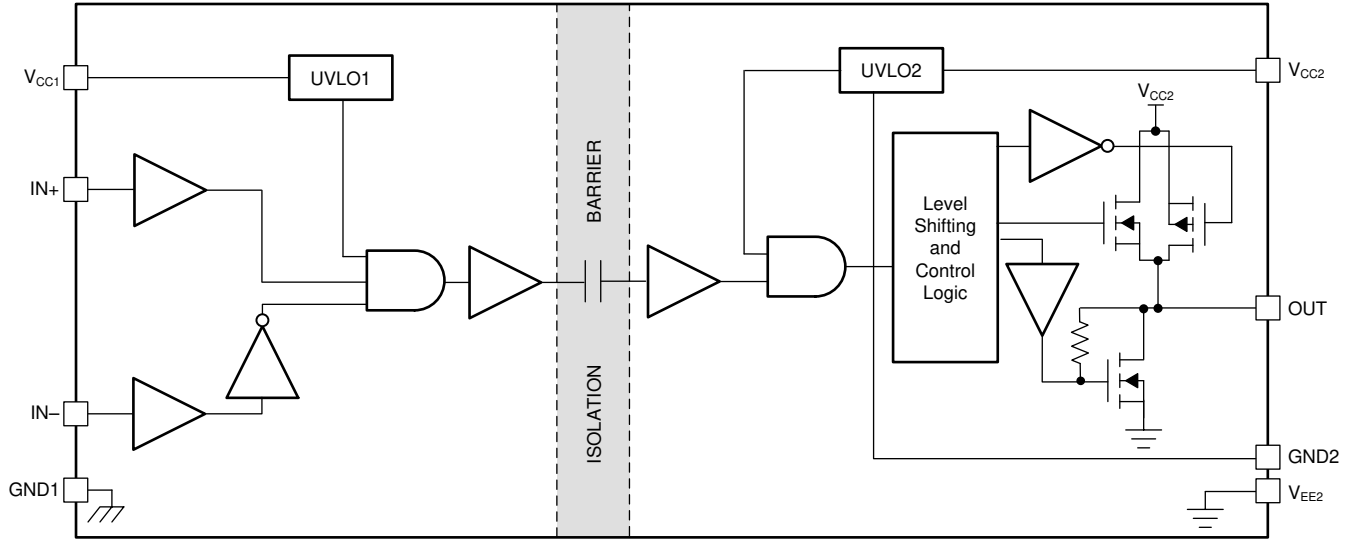
**図 8-2. On-Off Keying (OOK) Based Modulation Scheme**



☒ 8-3. Functional Block Diagram — Split Output (UCC53x0S)



☒ 8-4. Functional Block Diagram — Miller Clamp (UCC53x0M)




**8-5. Functional Block Diagram — UVLO With Respect to GND2 (UCC53x0E)**

## 8.3 Feature Description

### 8.3.1 Power Supply

The  $V_{CC1}$  input power supply supports a wide voltage range from 3 V to 15 V and the  $V_{CC2}$  output supply supports a voltage range from 9.5 V to 33 V. For operation with bipolar supplies, the power device is turned off with a negative voltage on the gate with respect to the emitter or source. This configuration prevents the power device from unintentionally turning on because of current induced from the Miller effect. The typical values of the  $V_{CC2}$  and  $V_{EE2}$  output supplies for bipolar operation are 15 V and  $-8$  V with respect to GND2 for IGBTs and 20 V and  $-5$  V for SiC MOSFETs.

For operation with unipolar supply, the  $V_{CC2}$  supply is connected to 15 V with respect to  $V_{EE2}$  for IGBTs, and 20 V for SiC MOSFETs. The  $V_{EE2}$  supply is connected to 0 V. In this use case, the UCC53x0 device with Miller clamping function (UCC53x0M) can be used. The Miller clamping function is implemented by adding a low impedance path between the gate of the power device and the  $V_{EE2}$  supply. Miller current sinks through the clamp pin, which clamps the gate voltage to be lower than the turn-on threshold value for the gate.

### 8.3.2 Input Stage

The input pins (IN+ and IN-) of the UCC53x0 family are based on CMOS-compatible input-threshold logic that is completely isolated from the  $V_{CC2}$  supply voltage. The input pins are easy to drive with logic-level control signals (such as those from 3.3-V microcontrollers), because the UCC53x0 family has a typical high threshold ( $V_{IT+(IN)}$ ) of  $0.55 \times V_{CC1}$  and a typical low threshold of  $0.45 \times V_{CC1}$ . A wide hysteresis ( $V_{hys(IN)}$ ) of  $0.1 \times V_{CC1}$  makes for good noise immunity and stable operation. If either of the inputs are left open, 128 k $\Omega$  of internal pull-down resistance forces the IN+ pin low and 128 k $\Omega$  of internal resistance pulls IN- high. However, TI still recommends grounding an input or tying to  $V_{CC1}$  if it is not being used for improved noise immunity.

Because the input side of the UCC53x0 family is isolated from the output driver, the input signal amplitude can be larger or smaller than  $V_{CC2}$  provided that it does not exceed the recommended limit. This feature allows greater flexibility when integrating the gate-driver with control signal sources and allows the user to choose the most efficient  $V_{CC2}$  for any gate. However, the amplitude of any signal applied to IN+ or IN- must never be at a voltage higher than  $V_{CC1}$ .

### 8.3.3 Output Stage

The output stages of the UCC53x0 family feature a pull-up structure that delivers the highest peak-source current when it is most needed which is during the Miller plateau region of the power-switch turn-on transition (when the power-switch drain or collector voltage experiences  $dV/dt$ ). The output stage pull-up structure features a P-channel MOSFET and an additional pull-up N-channel MOSFET in parallel. The function of the N-channel MOSFET is to provide a brief boost in the peak-sourcing current, which enables fast turn-on. Fast turn-on is accomplished by briefly turning on the N-channel MOSFET during a narrow instant when the output is changing states from low to high. 表 8-1 lists the typical internal resistance values of the pull-up and pull-down structure.

表 8-1. UCC53x0 On-Resistance

DEVICE OPTION	$R_{NMOS}$	$R_{OH}$	$R_{OL}$	$R_{CLAMP}$	UNIT
UCC5320SC and UCC5320EC	4.5	12	0.65	Not applicable	$\Omega$
UCC5310MC	4.5	12	1.3	1.3	$\Omega$
UCC5390SC and UCC5390EC	0.76	12	0.13	Not applicable	$\Omega$
UCC5350MC	1.54	12	0.26	0.26	$\Omega$
UCC5350SB	1.54	12	0.26	Not applicable	$\Omega$

The  $R_{OH}$  parameter is a DC measurement and is representative of the on-resistance of the P-channel device only. This parameter is only for the P-channel device, because the pull-up N-channel device is held in the OFF state in DC condition and is turned on only for a brief instant when the output is changing states from low to high. Therefore, the effective resistance of the UCC53x0 pull-up stage during this brief turn-on phase is much lower than what is represented by the  $R_{OH}$  parameter, which yields a faster turn-on. The turn-on-phase output resistance is the parallel combination  $R_{OH} \parallel R_{NMOS}$ .

The pull-down structure in the UCC53x0 S and E versions is simply composed of an N-channel MOSFET. For the M version, an additional FET is connected in parallel with the pull-down structure when the CLAMP and OUT pins are connected to the gate of the IGBT or MOSFET. The output voltage swing between  $V_{CC2}$  and  $V_{EE2}$  provides rail-to-rail operation.

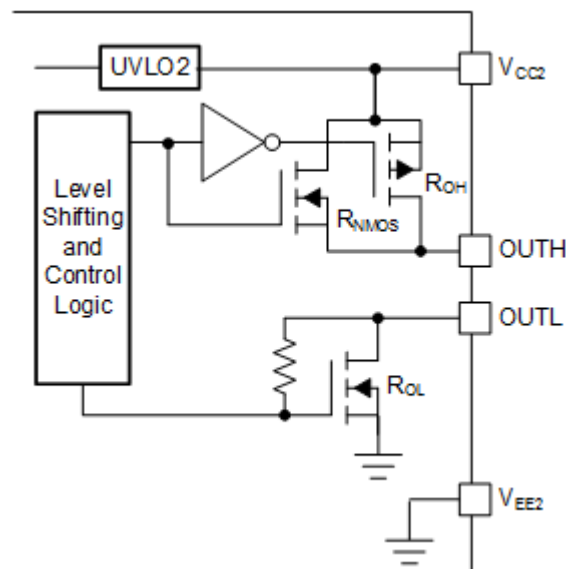


図 8-6. Output Stage—S Version

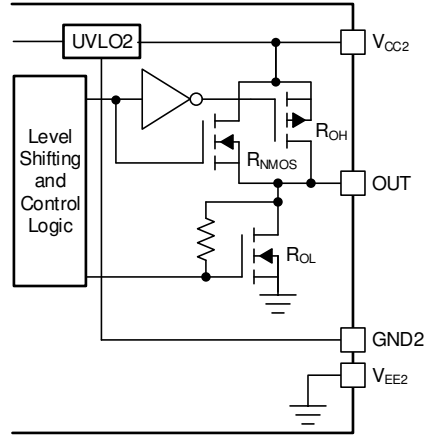


図 8-7. Output Stage—E Version

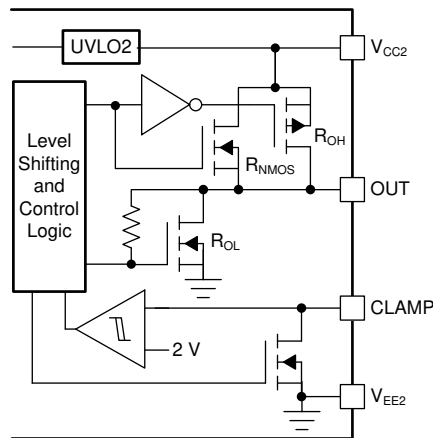


図 8-8. Output Stage—M Version

### 8.3.4 Protection Features

#### 8.3.4.1 Undervoltage Lockout (UVLO)

UVLO functions are implemented for both the  $V_{CC1}$  and  $V_{CC2}$  supplies between the  $V_{CC1}$  and  $GND1$ , and  $V_{CC2}$  and  $V_{EE2}$  pins to prevent an underdriven condition on IGBTs and MOSFETs. When  $V_{CC}$  is lower than  $V_{IT+}(UVLO)$  at device start-up or lower than  $V_{IT-}(UVLO)$  after start-up, the voltage-supply UVLO feature holds the effected output low, regardless of the input pins ( $IN+$  and  $IN-$ ) as shown in 表 8-2. The  $V_{CC}$  UVLO protection has a hysteresis feature ( $V_{hys}(UVLO)$ ). This hysteresis prevents chatter when the power supply produces ground noise; this allows the device to permit small drops in bias voltage, which occurs when the device starts switching and operating current consumption increases suddenly. 図 8-9 shows the UVLO functions.

表 8-2. UCC53x0  $V_{CC1}$  UVLO Logic

CONDITION	INPUTS		OUTPUTS	
	IN+	IN-	OUTH	OUT, OUTL
$V_{CC1} - GND1 < V_{IT+}(UVLO1)$ during device start-up	H	L	Hi-Z	L
	L	H	Hi-Z	L
	H	H	Hi-Z	L
	L	L	Hi-Z	L

表 8-2. UCC53x0 V<sub>CC1</sub> UVLO Logic (続き)

CONDITION	INPUTS		OUTPUTS	
	IN+	IN–	OUTH	OUT, OUTL
$V_{CC1} - GND1 < V_{IT-(UVLO1)}$ after device start-up	H	L	Hi-Z	L
	L	H	Hi-Z	L
	H	H	Hi-Z	L
	L	L	Hi-Z	L

表 8-3. UCC53x0 V<sub>CC2</sub> UVLO Logic

CONDITION	INPUTS		OUTPUTS	
	IN+	IN–	OUTH	OUT, OUTL
$V_{CC2} - V_{EE2} < V_{IT+(UVLO2)}$ during device start-up	H	L	Hi-Z	L
	L	H	Hi-Z	L
	H	H	Hi-Z	L
	L	L	Hi-Z	L
$V_{CC2} - V_{EE2} < V_{IT-(UVLO2)}$ after device start-up	H	L	Hi-Z	L
	L	H	Hi-Z	L
	H	H	Hi-Z	L
	L	L	Hi-Z	L

When  $V_{CC1}$  or  $V_{CC2}$  drops below the UVLO1 or UVLO2 threshold, a delay,  $t_{UVLO1\_rec}$  or  $t_{UVLO2\_rec}$ , occurs on the output when the supply voltage rises above  $V_{IT+(UVLO)}$  or  $V_{IT+(UVLO2)}$  again. 図 8-9 shows this delay.

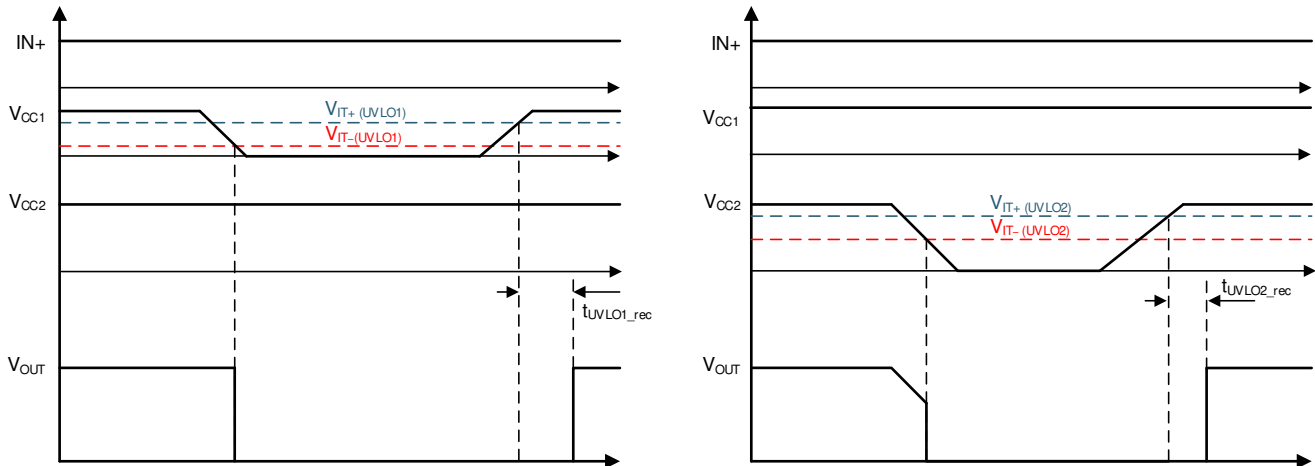


図 8-9. UVLO Functions

### 8.3.4.2 Active Pull-down


The active pull-down function is used to pull the IGBT or MOSFET gate to the low state when no power is connected to the  $V_{CC2}$  supply. This feature prevents false IGBT and MOSFET turn-on on the OUT and CLAMP pins by clamping the output to approximately 2 V.

When the output stages of the driver are in an unbiased or UVLO condition, the driver outputs are held low by an active clamp circuit that limits the voltage rise on the driver outputs. In this condition, the upper PMOS is resistively held off by a pull-up resistor while the lower NMOS gate is tied to the driver output through a 500-kΩ resistor. In this configuration, the output is effectively clamped to the threshold voltage of the lower NMOS device, which is approximately 1.5 V when no bias power is available.

### 8.3.4.3 Short-Circuit Clamping

The short-circuit clamping function is used to clamp voltages at the driver output and pull the active Miller clamp pins slightly higher than the  $V_{CC2}$  voltage during short-circuit conditions. The short-circuit clamping function helps protect the IGBT or MOSFET gate from overvoltage breakdown or degradation. The short-circuit clamping function is implemented by adding a diode connection between the dedicated pins and the  $V_{CC2}$  pin inside the driver. The internal diodes can conduct up to 500-mA current for a duration of 10  $\mu$ s and a continuous current of 20 mA. Use external Schottky diodes to improve current conduction capability as needed.

### 8.3.4.4 Active Miller Clamp (UCC53x0M)

The active Miller-clamp function helps to prevent a false turn-on of the power switches caused by Miller current in applications where a unipolar power supply is used. The active Miller-clamp function is implemented by adding a low impedance path between the power-switch gate terminal and ground ( $V_{EE2}$ ) to sink the Miller current. With the Miller-clamp function, the power-switch gate voltage is clamped to less than 2 V during the off state.  9-2 shows a typical application circuit of UCC5310M and UCC5350M.

## 8.4 Device Functional Modes

表 8-4 lists the functional modes for the UCC53x0 devices assuming  $V_{CC1}$  and  $V_{CC2}$  are in the recommended range.


**表 8-4. Function Table for UCC53x0S**

IN+	IN-	OUTH	OUTL
Low	X	Hi-Z	Low
X	High	Hi-Z	Low
High	Low	High	High-Z

**表 8-5. Function Table for UCC53x0M and UCC53x0E**

IN+	IN-	OUT
Low	X	Low
X	High	Low
High	Low	High

### 8.4.1 ESD Structure

 8-10 shows the multiple diodes involved in the ESD protection components of the UCC53x0 devices. This provides pictorial representation of the absolute maximum rating for the device.

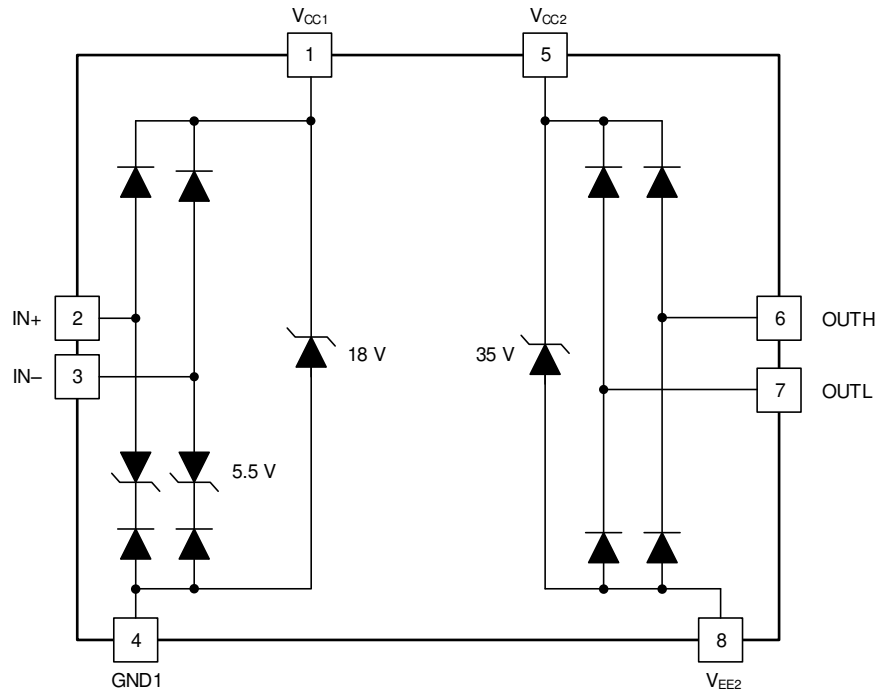


図 8-10. ESD Structure



## 9 Application and Implementation

### 注

以下のアプリケーション情報は、TI の製品仕様に含まれるものではなく、TI ではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくこととなります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

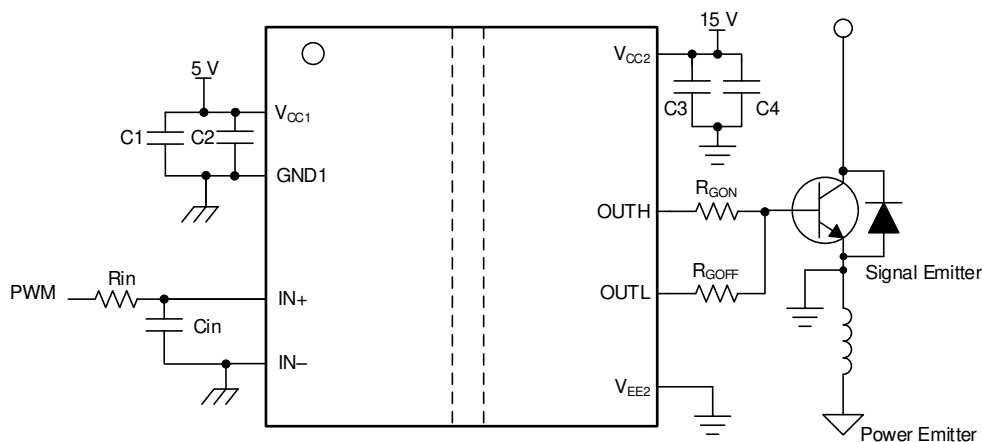
### 9.1 Application Information

The UCC53x0 is a family of simple, isolated gate drivers for power semiconductor devices, such as MOSFETs, IGBTs, or SiC MOSFETs. The family of devices is intended for use in applications such as motor control, solar inverters, switched-mode power supplies, and industrial inverters.

The UCC53x0 family of devices has three pinout configurations, featuring split outputs, Miller clamp, and UVLO with reference to GND2. The UCC5320SC, UCC5350SB, and UCC5390SC have a split output, OUTH and OUTL. The two pins can be used to separately decouple the power transistor turnon and turnoff commutations. The UCC5310MC and UCC5350MC feature active Miller clamping, which can be used to prevent false turn-on of the power transistors induced by the Miller current. The UCC5320EC and UCC5390EC offer true UVLO protection by monitoring the voltage between the  $V_{CC2}$  and GND2 pins to prevent the power transistors from operating in a saturation region. The UCC53x0 family of devices comes in an 8-pin D and 8-pin DWV package options and have a creepage, or clearance, of 4 mm and 8.5 mm respectively, which are suitable for applications where basic or reinforced isolation is required. Different drive strengths enable a simple driver platform to be used for applications demanding power transistors with different power ratings. Specifically, the UCC5390 device offers a 10-A minimum drive current which can help remove the external current buffer used to drive high power transistors.

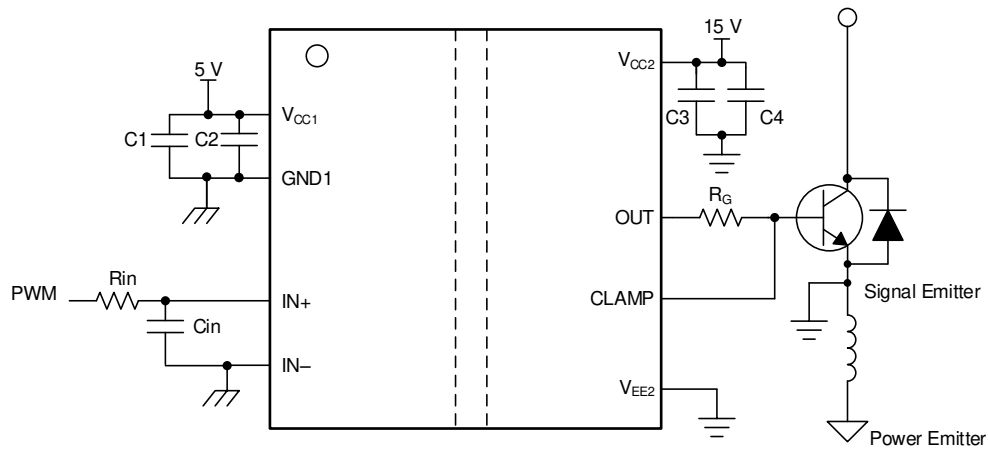
### 9.2 Typical Application

The circuits in [Figure 9-1](#), [Figure 9-2](#), and [Figure 9-3](#) show a typical application for driving IGBTs.



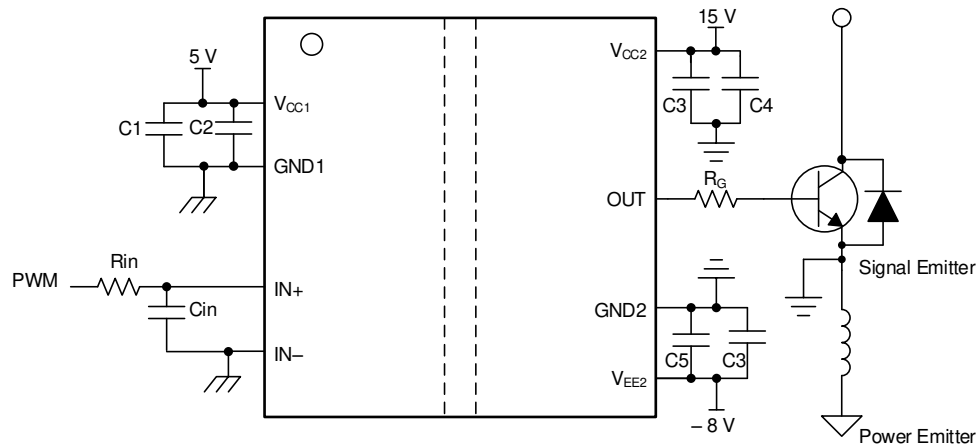
Copyright © 2017, Texas Instruments Incorporated

**Figure 9-1. Typical Application Circuit for UCC53x0S to Drive IGBT**



Copyright © 2017, Texas Instruments Incorporated

**図 9-2. Typical Application Circuit for UCC5310M and UCC5350M to Drive IGBT**



Copyright © 2018, Texas Instruments Incorporated

**図 9-3. Typical Application Circuit for UCC5320E and UCC5390E to Drive IGBT**

### 9.2.1 Design Requirements

表 9-1 lists the recommended conditions to observe the input and output of the UCC5320S split-output gate driver with the IN– pin tied to the GND1 pin.

**表 9-1. UCC5320S Design Requirements**

PARAMETER	VALUE	UNIT
V <sub>CC1</sub>	3.3	V
V <sub>CC2</sub>	15	V
IN+	3.3	V
IN–	GND1	-
Switching frequency	10	kHz
IGBT	IKW50N65H5	-

## 9.2.2 Detailed Design Procedure

### 9.2.2.1 Designing $IN+$ and $IN-$ Input Filter

TI recommends that users avoid shaping the signals to the gate driver in an attempt to slow down (or delay) the signal at the output. However, a small input filter,  $R_{IN}$ - $C_{IN}$ , can be used to filter out the ringing introduced by nonideal layout or long PCB traces.

Such a filter should use an  $R_{IN}$  resistor with a value from 0  $\Omega$  to 100  $\Omega$  and a  $C_{IN}$  capacitor with a value from 10 pF to 1000 pF. In the example, the selected value for  $R_{IN}$  is 51  $\Omega$  and  $C_{IN}$  is 33 pF, with a corner frequency of approximately 100 MHz.

When selecting these components, pay attention to the trade-off between good noise immunity and propagation delay.

### 9.2.2.2 Gate-Driver Output Resistor

The external gate-driver resistors,  $R_{G(ON)}$  and  $R_{G(OFF)}$  are used to:

1. Limit ringing caused by parasitic inductances and capacitances
2. Limit ringing caused by high voltage or high current switching  $dv/dt$ ,  $di/dt$ , and body-diode reverse recovery
3. Fine-tune gate drive strength, specifically peak sink and source current to optimize the switching loss
4. Reduce electromagnetic interference (EMI)

The output stage has a pull-up structure consisting of a P-channel MOSFET and an N-channel MOSFET in parallel. The combined peak source current is 4.3 A for the UCC5320 family and 17 A for the UCC5390 family and 17 A for the UCC5390 family. Use 式 1 to estimate the peak source current using the UCC5320S as an example.

$$I_{OH} = \min \left( 4.3 \text{ A}, \frac{V_{CC2}}{R_{NMOS} \parallel R_{OH} + R_{ON} + R_{GFET\_Int}} \right) \quad (1)$$

where

- $R_{ON}$  is the external turn-on resistance.
- $R_{GFET\_Int}$  is the power transistor internal gate resistance, found in the power transistor data sheet. We will assume 0 $\Omega$  for our example.
- $I_{OH}$  is the peak source current which is the minimum value between 4.3 A, the gate-driver peak source current, and the calculated value based on the gate-drive loop resistance.

In this example, the peak source current is approximately 1.8 A as calculated in 式 2.

$$I_{OH} = \frac{V_{CC2}}{R_{NMOS} \parallel R_{OH} + R_{ON} + R_{GFET\_Int}} = \frac{15 \text{ V}}{4.5 \Omega \parallel 12 \Omega + 5.1 \Omega + 0 \Omega} \approx 1.8 \text{ A} \quad (2)$$

Similarly, use 式 3 to calculate the peak sink current.

$$I_{OL} = \min \left( 4.4 \text{ A}, \frac{V_{CC2}}{R_{OL} + R_{OFF} + R_{GFET\_Int}} \right) \quad (3)$$

where

- $R_{OFF}$  is the external turn-off resistance.
- $I_{OL}$  is the peak sink current which is the minimum value between 4.4 A, the gate-driver peak sink current, and the calculated value based on the gate-drive loop resistance.

In this example, the peak sink current is the minimum value between 式 4 and 4.4 A.

$$I_{OL} = \frac{V_{CC2}}{R_{OL} + R_{OFF} + R_{GFET\_Int}} = \frac{15 \text{ V}}{0.65 \Omega + 10 \Omega + 0 \Omega} \approx 1.4 \text{ A} \quad (4)$$

注

The estimated peak current is also influenced by PCB layout and load capacitance. Parasitic inductance in the gate-driver loop can slow down the peak gate-drive current and introduce overshoot and undershoot. Therefore, TI strongly recommends that the gate-driver loop should be minimized. Conversely, the peak source and sink current is dominated by loop parasitics when the load capacitance ( $C_{ISS}$ ) of the power transistor is very small (typically less than 1 nF) because the rising and falling time is too small and close to the parasitic ringing period.

### 9.2.2.3 Estimate Gate-Driver Power Loss

The total loss,  $P_G$ , in the gate-driver subsystem includes the power losses ( $P_{GD}$ ) of the UCC53x0 device and the power losses in the peripheral circuitry, such as the external gate-drive resistor.

The  $P_{GD}$  value is the key power loss which determines the thermal safety-related limits of the UCC53x0 device, and it can be estimated by calculating losses from several components.

The first component is the static power loss,  $P_{GDQ}$ , which includes quiescent power loss on the driver as well as driver self-power consumption when operating with a certain switching frequency. The  $P_{GDQ}$  parameter is measured on the bench with no load connected to the OUT or OUTH and OUTL pins at a given  $V_{CC1}$ ,  $V_{CC2}$ , switching frequency, and ambient temperature. In this example,  $V_{CC1}$  is 3.3V and  $V_{CC2}$  is 15 V. The current on each power supply, with PWM switching from 0 V to 3.3 V at 10 kHz, is measured to be  $I_{CC1} = 1.67 \text{ mA}$  and  $I_{CC2} = 1.11 \text{ mA}$ . Therefore, use 式 5 to calculate  $P_{GDQ}$ .

$$P_{GDQ} = V_{CC1} \times I_{VCC1} + V_{CC2} \times I_{CC2} \approx 22 \text{ mW} \quad (5)$$

The second component is the switching operation loss,  $P_{GDO}$ , with a given load capacitance which the driver charges and discharges the load during each switching cycle. Use 式 6 to calculate the total dynamic loss from load switching,  $P_{GSW}$ .

$$P_{GSW} = V_{CC2} \times Q_G \times f_{SW} \quad (6)$$

where

- $Q_G$  is the gate charge of the power transistor at  $V_{CC2}$ .

So, for this example application the total dynamic loss from load switching is approximately 18 mW as calculated in 式 7.

$$P_{GSW} = 15 \text{ V} \times 120 \text{ nC} \times 10 \text{ kHz} = 18 \text{ mW} \quad (7)$$

$Q_G$  represents the total gate charge of the power transistor switching 520 V at 50 A, and is subject to change with different testing conditions. The UCC5320S gate-driver loss on the output stage,  $P_{GDO}$ , is part of  $P_{GSW}$ .  $P_{GDO}$  is equal to  $P_{GSW}$  if the external gate-driver resistance and power-transistor internal resistance are 0  $\Omega$ , and all the gate driver-loss will be dissipated inside the UCC5320S. If an external turn-on and turn-off resistance exists, the total loss is distributed between the gate driver pull-up/down resistance, external gate resistance, and power-transistor internal resistance. Importantly, the pull-up/down resistance is a linear and fixed resistance if the source/sink current is not saturated to 4.3 A/4.4 A, however, it will be non-linear if the source/sink current is saturated. Therefore,  $P_{GDO}$  is different in these two scenarios.

#### Case 1 - Linear Pull-Up/Down Resistor:

$$P_{GDO} = \frac{P_{GSW}}{2} \left( \frac{R_{OH} \parallel R_{NMOS}}{R_{OH} \parallel R_{NMOS} + R_{ON} + R_{GFET\_Int}} + \frac{R_{OL}}{R_{OL} + R_{OFF} + R_{GFET\_Int}} \right) \quad (8)$$

In this design example, all the predicted source and sink currents are less than 4.3 A and 4.4 A, therefore, use 式 9 to estimate the UCC53x0 gate-driver loss.

$$P_{GDO} = \frac{18 \text{ mW}}{2} \left( \frac{12 \Omega \parallel 4.5 \Omega}{12 \Omega \parallel 4.5 \Omega + 5.1 \Omega + 0 \Omega} + \frac{0.65 \Omega}{0.65 \Omega + 10 \Omega + 0 \Omega} \right) \approx 4.1 \text{ mW} \quad (9)$$

### Case 2 - Nonlinear Pull-Up/Down Resistor:

$$P_{GDO} = f_{SW} \times \left[ 4.3 \text{ A} \times \int_0^{T_{R\_Sys}} (V_{CC2} - V_{OUTH}(t)) dt + 4.4 \text{ A} \times \int_0^{T_{F\_Sys}} V_{OUTL}(t) dt \right] \quad (10)$$

where

- $V_{OUTH/L}(t)$  is the gate-driver OUTH and OUTL pin voltage during the turnon and turnoff period. In cases where the output is saturated for some time, this value can be simplified as a constant-current source (4.3 A at turnon and 4.4 A at turnoff) charging or discharging a load capacitor. Then, the  $V_{OUTH/L}(t)$  waveform will be linear and the  $T_{R\_Sys}$  and  $T_{F\_Sys}$  can be easily predicted.

For some scenarios, if only one of the pull-up or pull-down circuits is saturated and another one is not, the  $P_{GDO}$  is a combination of case 1 and case 2, and the equations can be easily identified for the pull-up and pull-down based on this discussion.

Use 式 11 to calculate the total gate-driver loss dissipated in the UCC53x0 gate driver,  $P_{GD}$ .

$$P_{GD} = P_{GDQ} + P_{GDO} = 22 \text{ mW} + 4.1 \text{ mW} = 26.1 \text{ mW} \quad (11)$$

### 9.2.2.4 Estimating Junction Temperature

Use the equation below to estimate the junction temperature ( $T_J$ ) of the UCC53x0 family.

$$T_J = T_C + \Psi_{JT} \times P_{GD} \quad (12)$$

where

- $T_C$  is the UCC53x0 case-top temperature measured with a thermocouple or some other instrument.
- $\Psi_{JT}$  is the junction-to-top characterization parameter from the Thermal Information table.

Using the junction-to-top characterization parameter ( $\Psi_{JT}$ ) instead of the junction-to-case thermal resistance ( $R_{\theta JC}$ ) can greatly improve the accuracy of the junction temperature estimation. The majority of the thermal energy of most ICs is released into the PCB through the package leads, whereas only a small percentage of the total energy is released through the top of the case (where thermocouple measurements are usually conducted). The  $R_{\theta JC}$  resistance can only be used effectively when most of the thermal energy is released through the case, such as with metal packages or when a heat sink is applied to an IC package. In all other cases, use of  $R_{\theta JC}$  will inaccurately estimate the true junction temperature. The  $\Psi_{JT}$  parameter is experimentally derived by assuming that the dominant energy leaving through the top of the IC will be similar in both the testing environment and the application environment. As long as the recommended layout guidelines are observed, junction temperature estimations can be made accurately to within a few degrees Celsius.

### 9.2.3 Selecting $V_{CC1}$ and $V_{CC2}$ Capacitors

Bypass capacitors for the  $V_{CC1}$  and  $V_{CC2}$  supplies are essential for achieving reliable performance. TI recommends choosing low-ESR and low-ESL, surface-mount, multi-layer ceramic capacitors (MLCC) with sufficient voltage ratings, temperature coefficients, and capacitance tolerances.

注

DC bias on some MLCCs will impact the actual capacitance value. For example, a 25-V, 1- $\mu$ F X7R capacitor is measured to be only 500 nF when a DC bias of 15- $V_{DC}$  is applied.

#### 9.2.3.1 Selecting a $V_{CC1}$ Capacitor

A bypass capacitor connected to the  $V_{CC1}$  pin supports the transient current required for the primary logic and the total current consumption, which is only a few milliamperes. Therefore, a 50-V MLCC with over 100 nF is recommended for this application. If the bias power-supply output is located a relatively long distance from the  $V_{CC1}$  pin, a tantalum or electrolytic capacitor with a value greater than 1  $\mu$ F should be placed in parallel with the MLCC.

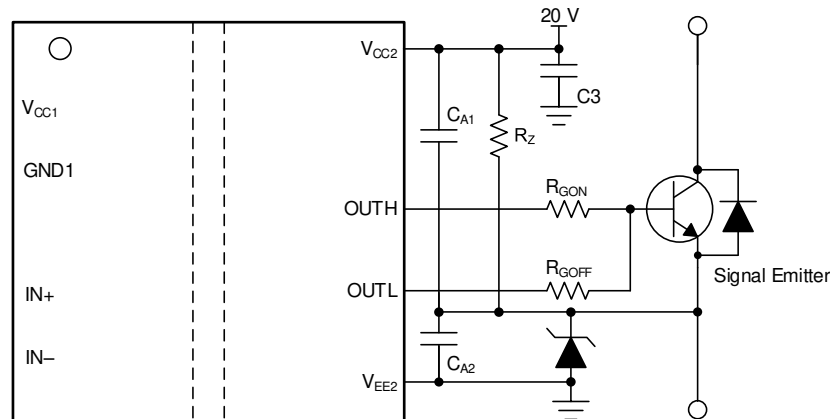
#### 9.2.3.2 Selecting a $V_{CC2}$ Capacitor

A 50-V, 10- $\mu$ F MLCC and a 50-V, 0.22- $\mu$ F MLCC are selected for the  $C_{VCC2}$  capacitor. If the bias power supply output is located a relatively long distance from the  $V_{CC2}$  pin, a tantalum or electrolytic capacitor with a value greater than 10  $\mu$ F should be used in parallel with  $C_{VCC2}$ .

#### 9.2.3.3 Application Circuits with Output Stage Negative Bias

When parasitic inductances are introduced by nonideal PCB layout and long package leads (such as TO-220 and TO-247 type packages), ringing in the gate-source drive voltage of the power transistor could occur during high di/dt and dv/dt switching. If the ringing is over the threshold voltage, unintended turn-on and shoot-through could occur. Applying a negative bias on the gate drive is a popular way to keep such ringing below the threshold. A few examples of implementing negative gate-drive bias follow.

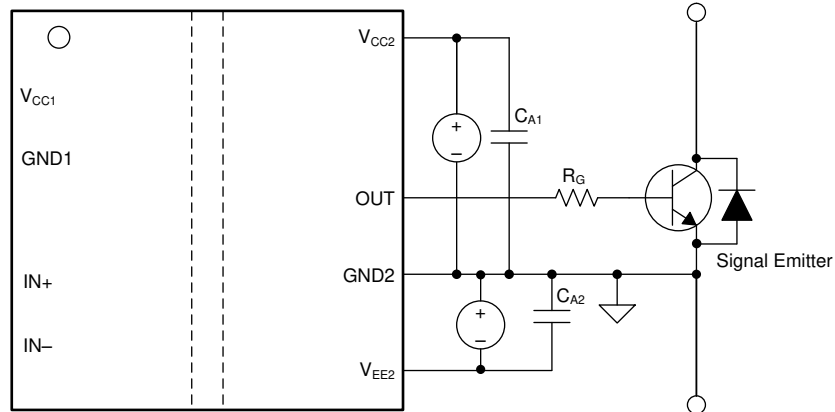
Figure 9-4 shows the first example with negative bias turn-off on the output using a Zener diode on the isolated power-supply output stage. The negative bias is set by the Zener diode voltage. If the isolated power supply is equal to 20 V, the turn-off voltage is  $-5.1$  V and the turn-on voltage is  $20$  V  $- 5.1$  V  $\approx 15$  V.



Copyright © 2017, Texas Instruments Incorporated

Figure 9-4. Negative Bias With Zener Diode on Iso-Bias Power-Supply Output

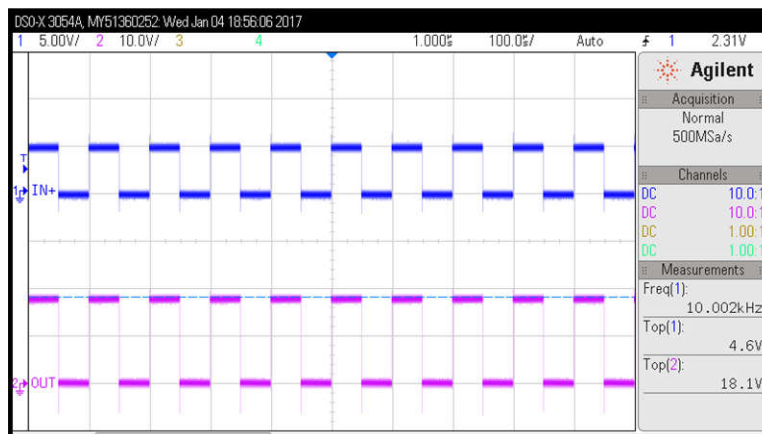
Figure 9-5 shows another example which uses two supplies (or single-input, double-output power supply). The power supply across  $V_{CC2}$  and  $GND2$  determines the positive drive output voltage and the power supply across  $V_{EE2}$  and  $GND2$  determines the negative turn-off voltage. This solution requires more power supplies than the first example, however, it provides more flexibility when setting the positive and negative rail voltages.



Copyright © 2017, Texas Instruments Incorporated

図 9-5. Negative Bias With Two Iso-Bias Power Supplies (UCC5320E and UCC5390E)

### 9.2.4 Application Curve



$V_{CC2} = 20\text{ V}$        $V_{EE2} = \text{GND}$        $f_{\text{SW}} = 10\text{ kHz}$

図 9-6. PWM Input and Gate Voltage Waveform

## 10 Power Supply Recommendations

The recommended input supply voltage ( $V_{CC1}$ ) for the UCC53x0 device is from 3 V to 15 V. The lower limit of the range of output bias-supply voltage ( $V_{CC2}$ ) is determined by the internal UVLO protection feature of the device. The  $V_{CC1}$  and  $V_{CC2}$  voltages should not fall below their respective UVLO thresholds for normal operation, or else the gate-driver outputs can become clamped low for more than 50  $\mu\text{s}$  by the UVLO protection feature. For more information on UVLO, see [セクション 8.3.4.1](#). The higher limit of the  $V_{CC2}$  range depends on the maximum gate voltage of the power device that is driven by the UCC53x0 device, and should not exceed the recommended maximum  $V_{CC2}$  of 33 V. A local bypass capacitor should be placed between the  $V_{CC2}$  and  $V_{EE2}$  pins, with a value of 220-nF to 10- $\mu\text{F}$  for device biasing. TI recommends placing an additional 100-nF capacitor in parallel with the device biasing capacitor for high frequency filtering. Both capacitors should be positioned as close to the device as possible. Low-ESR, ceramic surface-mount capacitors are recommended. Similarly, a bypass capacitor should also be placed between the  $V_{CC1}$  and GND1 pins. Given the small amount of current drawn by the logic circuitry within the input side of the UCC53x0 device, this bypass capacitor has a minimum recommended value of 100 nF.

If only a single, primary-side power supply is available in an application, isolated power can be generated for the secondary side with the help of a transformer driver such as Texas Instruments' [SN6501](#) or [SN6505A](#). For such

applications, detailed power supply design and transformer selection recommendations are available in [SN6501 Transformer Driver for Isolated Power Supplies data sheet](#) and [SN6505A Low-Noise 1-A Transformer Drivers for Isolated Power Supplies data sheet](#).

## 11 Layout


### 11.1 Layout Guidelines

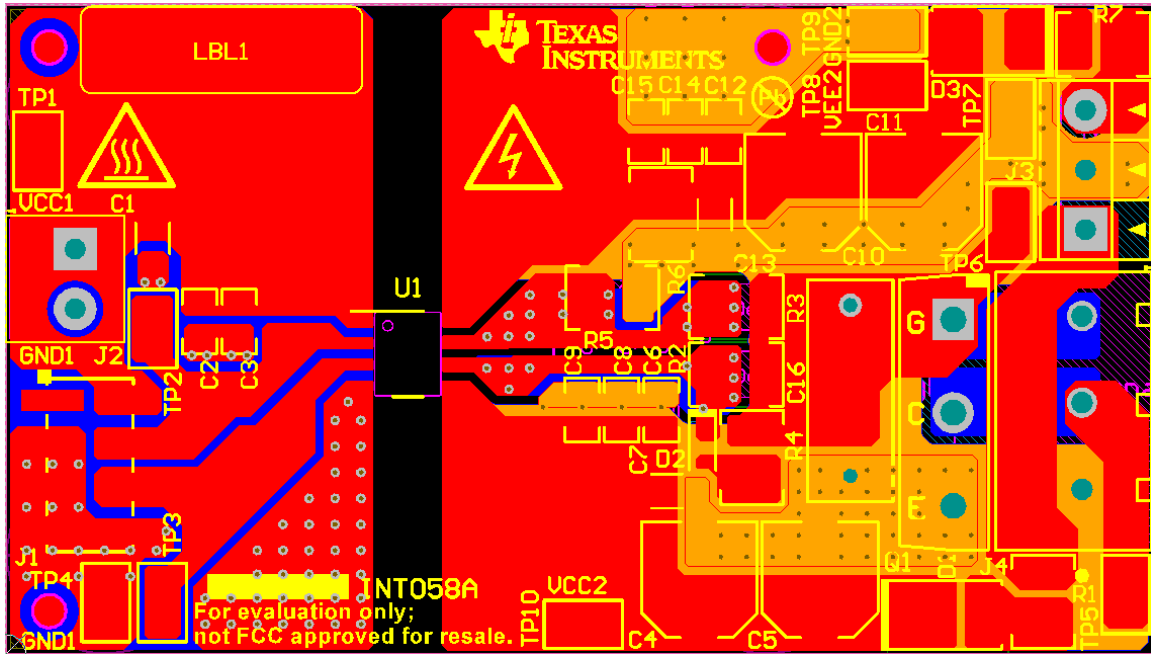
Designers must pay close attention to PCB layout to achieve optimum performance for the UCC53x0. Some key guidelines are:

- Component placement:
  - Low-ESR and low-ESL capacitors must be connected close to the device between the  $V_{CC1}$  and GND1 pins and between the  $V_{CC2}$  and  $V_{EE2}$  pins to bypass noise and to support high peak currents when turning on the external power transistor.
  - To avoid large negative transients on the  $V_{EE2}$  pins connected to the switch node, the parasitic inductances between the source of the top transistor and the source of the bottom transistor must be minimized.
- Grounding considerations:
  - Limiting the high peak currents that charge and discharge the transistor gates to a minimal physical area is essential. This limitation decreases the loop inductance and minimizes noise on the gate terminals of the transistors. The gate driver must be placed as close as possible to the transistors.
- High-voltage considerations:
  - To ensure isolation performance between the primary and secondary side, avoid placing any PCB traces or copper below the driver device. A PCB cutout or groove is recommended in order to prevent contamination that may compromise the isolation performance.
- Thermal considerations:
  - A large amount of power may be dissipated by the UCC53x0 if the driving voltage is high, the load is heavy, or the switching frequency is high (for more information, see [セクション 9.2.2.3](#)). Proper PCB layout can help dissipate heat from the device to the PCB and minimize junction-to-board thermal impedance ( $\theta_{JB}$ ).
  - Increasing the PCB copper connecting to the  $V_{CC2}$  and  $V_{EE2}$  pins is recommended, with priority on maximizing the connection to  $V_{EE2}$ . However, the previously mentioned high-voltage PCB considerations must be maintained.
  - If the system has multiple layers, TI also recommends connecting the  $V_{CC2}$  and  $V_{EE2}$  pins to internal ground or power planes through multiple vias of adequate size. These vias should be located close to the IC pins to maximize thermal conductivity. However, keep in mind that no traces or coppers from different high voltage planes are overlapping.





## 11.2 Layout Example

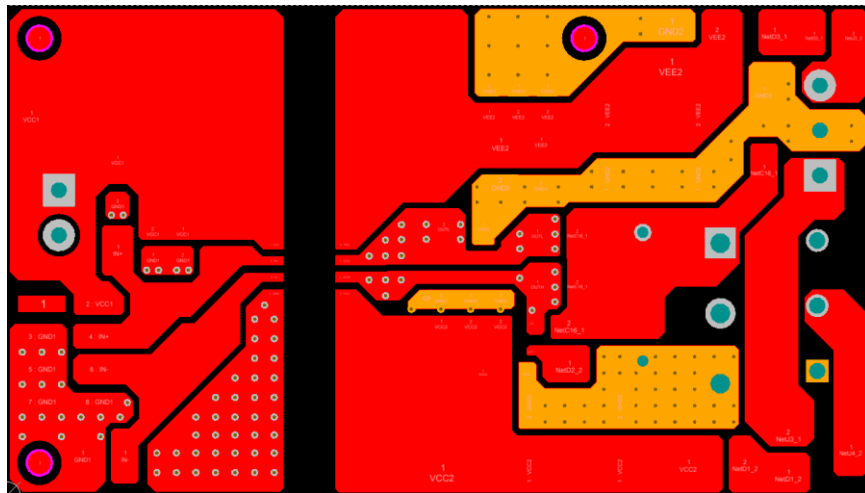
 11-1 shows a PCB layout example with the signals and key components labeled.



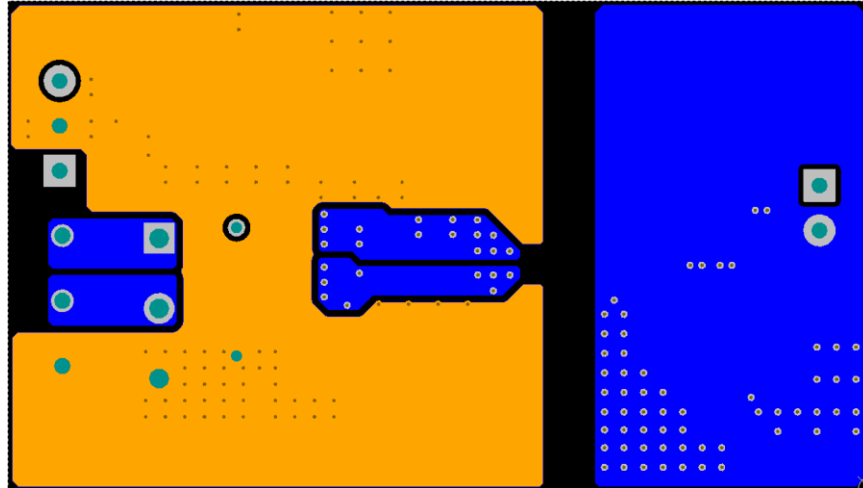
A. No PCB traces or copper are located between the primary and secondary side, which ensures isolation performance.

 11-1. Layout Example

 11-2 and  11-3 show the top and bottom layer traces and copper.

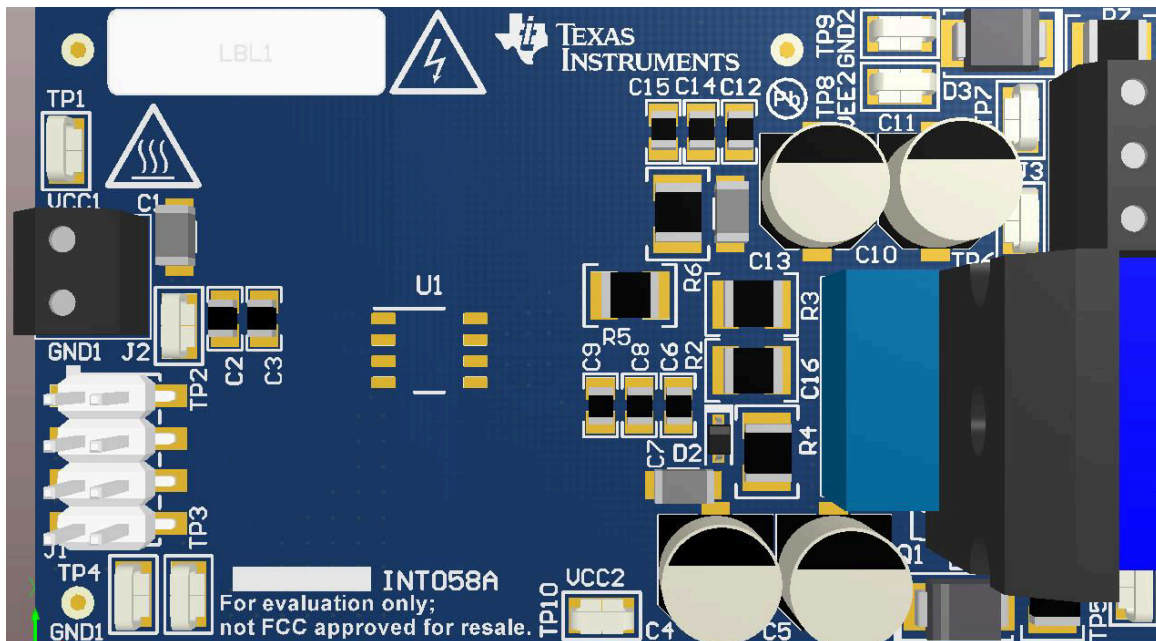


 11-2. Top-Layer Traces and Copper



☒ 11-3. Bottom-Layer Traces and Copper (Flipped)

☒ 11-4 shows the 3D layout of the top view of the PCB.



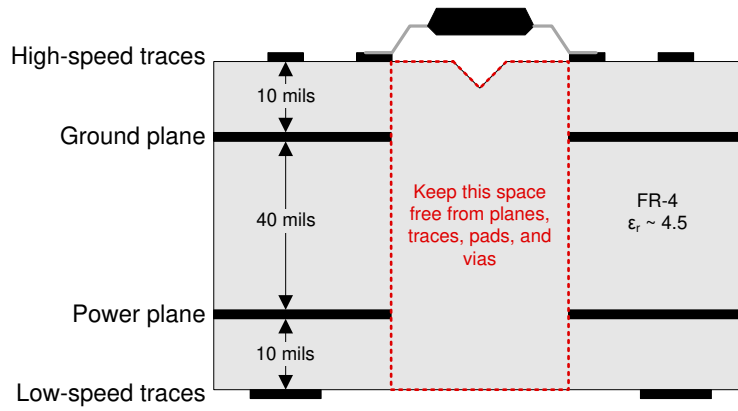
A. The location of the PCB cutout between primary side and secondary sides ensures isolation performance.

☒ 11-4. 3-D PCB View

### 11.3 PCB Material

Use standard FR-4 UL94V-0 printed circuit board. This PCB is preferred over cheaper alternatives because of lower dielectric losses at high frequencies, less moisture absorption, greater strength and stiffness, and the self-extinguishing flammability-characteristics.

☒ 11-5 shows the recommended layer stack.



☒ 11-5. Recommended Layer Stack

## 12 Device and Documentation Support

### 12.1 Device Support

#### 12.1.1 サード・パーティ製品に関する免責事項

サード・パーティ製品またはサービスに関するテキサス・インスツルメンツの出版物は、単独またはテキサス・インスツルメンツの製品、サービスと一緒に提供される場合に関係なく、サード・パーティ製品またはサービスの適合性に関する是認、サード・パーティ製品またはサービスの是認の表明を意味するものではありません。

### 12.2 Documentation Support

#### 12.2.1 Related Documentation

For related documentation see the following:

- Texas Instruments, [Digital Isolator Design Guide](#)
- Texas Instruments, [Isolation Glossary](#)
- Texas Instruments, [SN6501 Transformer Driver for Isolated Power Supplies data sheet](#)
- Texas Instruments, [SN6505A Low-Noise 1-A Transformer Drivers for Isolated Power Supplies data sheet](#)
- Texas Instruments, [UCC5390ECDWV Isolated Gate Driver Evaluation Module user's guide](#)
- Texas Instruments, [UCC53x0xD Evaluation Module user's guide](#)

### 12.3 Certifications

UL Online Certifications Directory, "[FPPT2.E181974 Nonoptical Isolating Devices - Component](#)" Certificate Number: 20170718-E181974,

### 12.4 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、[www.tij.co.jp](http://www.tij.co.jp) のデバイス製品フォルダを開いてください。[通知] をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取ることができます。変更の詳細については、改訂されたドキュメントに含まれている改訂履歴をご覧ください。

### 12.5 サポート・リソース

テキサス・インスツルメンツ E2E™ サポート・フォーラムは、エンジニアが検証済みの回答と設計に関するヒントをエキスパートから迅速かつ直接得ることができる場所です。既存の回答を検索したり、独自の質問をしたりすることで、設計に必要な支援を迅速に得ることができます。

リンクされているコンテンツは、各寄稿者により「現状のまま」提供されるものです。これらはテキサス・インスツルメンツの仕様を構成するものではなく、必ずしもテキサス・インスツルメンツの見解を反映したものではありません。テキサス・インスツルメンツの[使用条件](#)を参照してください。

### 12.6 Trademarks

テキサス・インスツルメンツ E2E™ is a trademark of Texas Instruments.  
すべての商標は、それぞれの所有者に帰属します。

### 12.7 静電気放電に関する注意事項



この IC は、ESD によって破損する可能性があります。テキサス・インスツルメンツは、IC を取り扱う際には常に適切な注意を払うことを推奨します。正しい取り扱いおよび設置手順に従わない場合、デバイスを破損するおそれがあります。

ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずかに変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

### 12.8 用語集

[テキサス・インスツルメンツ用語集](#) この用語集には、用語や略語の一覧および定義が記載されています。

## 13 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

**Changes from Revision H (February 2024) to Revision I (March 2024) Page**

- Changed Certification Planned to Certification number: 40047657 in Safety-Related Certifications For DWV Package section..... 10

**Changes from Revision G (December 2023) to Revision H (February 2024) Page**

- Changed CTI and Material Group values in insulation specifications and added table note.....8

**Changes from Revision F (January 2019) to Revision G (December 2023) Page**

- Added UCC5350MC DWV package.....3

**Changes from Revision E (October 2018) to Revision F (January 2019) Page**

- 2 番目の項目から (UCC5390EC) を削除(現在 3 つの幅広デバイスがリリースされているので)..... 1
- 安全関連認証に DIN EN 61010-1 を追加..... 1
- 「安全関連の認定」の箇条書き項目全体にわたって「(予定)」を追加..... 1
- 「概要」の「ピン配置構成と駆動力のバリエーション」とスイッチ タイプの情報を変更..... 1
- Changed creepage and clearance from 9 mm to 8.5 mm in Insulation Specifications and throughout datasheet..... 9
- Added VDE and CQC certification for D package and UL file number for DWV package ..... 10
- Changed test condition for  $V_{OH}$  ..... 11
- Changed a minor detail to the UCC53x0M figures.....28
- Changed typical application circuit for E Version to include capacitors on negative bias ..... 33

**Changes from Revision D (May 2018) to Revision E (October 2018) Page**

- Changed UCC5310 DWV package from Preview to Final..... 3
- Changed UCC5320 DWV package from Preview to Final..... 3

**Changes from Revision C (February 2018) to Revision D (May 2018) Page**

- UCC5390EC のマーケティング ステータスをプレビューから量産に変更..... 1

**Changes from Revision B (August 2017) to Revision C (February 2018) Page**

- UCC5350SBD、UCC5320SCDWV、UCC5310MCDWV、UCC5390ECDWV デバイスをデータシートに追加..... 1
- E および M バージョンと DWV パッケージの情報を含むように「特長」、「アプリケーション」、「概要」、「機能ブロック図」を変更..... 1
- Added UCC5350SB to the pin configuration and function.....4
- Added minimum storage temperature..... 6
- Changed from VDE V 0884-10 to VDE V 0884-11 in insulation specifications and safety-related certification table..... 8
- Changed safety limiting values..... 10
- Deleted test conditions for Supply Currents..... 11
- Added Typical Curves and Test Conditions to include UCC5390 and UCC5350 information..... 15
- Deleted device I/O figure ..... 31

• Changed ESD figure .....	31
• Added UL online certification directory to the certification section.....	44

---

**Changes from Revision A (June 2017) to Revision B (August 2017) Page**

---

• 動作時の周囲温度の最低値を -55°Cから -40°Cに変更.....	1
---------------------------------------	---

---

**Changes from Revision \* (June 2017) to Revision A (June 2017) Page**

---

• 将来の 10A デバイスにも利用可能な 17A をタイトルから削除.....	1
--	---

---

## 14 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

## 重要なお知らせと免責事項

テキサス・インスツルメンツは、技術データと信頼性データ(データシートを含みます)、設計リソース(リファレンス デザインを含みます)、アプリケーションや設計に関する各種アドバイス、Web ツール、安全性情報、その他のリソースを、欠陥が存在する可能性のある「現状のまま」提供しており、商品性および特定目的に対する適合性の黙示保証、第三者の知的財産権の非侵害保証を含むいかなる保証も、明示的または黙示的にかかわらず拒否します。

これらのリソースは、テキサス・インスツルメンツ製品を使用する設計の経験を積んだ開発者への提供を意図したものです。(1) お客様のアプリケーションに適したテキサス・インスツルメンツ製品の選定、(2) お客様のアプリケーションの設計、検証、試験、(3) お客様のアプリケーションに該当する各種規格や、その他のあらゆる安全性、セキュリティ、規制、または他の要件への確実な適合に関する責任を、お客様のみが単独で負うものとします。

上記の各種リソースは、予告なく変更される可能性があります。これらのリソースは、リソースで説明されているテキサス・インスツルメンツ製品を使用するアプリケーションの開発の目的でのみ、テキサス・インスツルメンツはその使用をお客様に許諾します。これらのリソースに関して、他の目的で複製することや掲載することは禁止されています。テキサス・インスツルメンツや第三者の知的財産権のライセンスが付与されている訳ではありません。お客様は、これらのリソースを自身で使用した結果発生するあらゆる申し立て、損害、費用、損失、責任について、テキサス・インスツルメンツおよびその代理人を完全に補償するものとし、テキサス・インスツルメンツは一切の責任を拒否します。

テキサス・インスツルメンツの製品は、[テキサス・インスツルメンツの販売条件](#)、または [ti.com](https://www.ti.com) やかかるテキサス・インスツルメンツ製品の関連資料などのいずれかを通じて提供する適用可能な条項の下で提供されています。テキサス・インスツルメンツがこれらのリソースを提供することは、適用されるテキサス・インスツルメンツの保証または他の保証の放棄の拡大や変更を意味するものではありません。

お客様がいかなる追加条項または代替条項を提案した場合でも、テキサス・インスツルメンツはそれらに異議を唱え、拒否します。

郵送先住所: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265  
Copyright © 2024, Texas Instruments Incorporated

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
UCC5310MCD	LIFEBUY	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	5310M	
UCC5310MCDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	5310M	Samples
UCC5310MCDWV	LIFEBUY	SOIC	DWV	8	64	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	5310MC	
UCC5310MCDWVR	ACTIVE	SOIC	DWV	8	1000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	5310MC	Samples
UCC5320ECD	LIFEBUY	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	5320E	
UCC5320ECDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	5320E	Samples
UCC5320SCD	LIFEBUY	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	5320S	
UCC5320SCDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	5320S	Samples
UCC5320SCDWV	LIFEBUY	SOIC	DWV	8	64	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	5320SC	
UCC5320SCDWVR	ACTIVE	SOIC	DWV	8	1000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	5320SC	Samples
UCC5350MCD	LIFEBUY	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	5350M	
UCC5350MCDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	5350M	Samples
UCC5350MCDWV	LIFEBUY	SOIC	DWV	8	64	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	5350MC	
UCC5350MCDWVR	ACTIVE	SOIC	DWV	8	1000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	5350MC	Samples
UCC5350SBD	LIFEBUY	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	5350SB	
UCC5350SBDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	5350SB	Samples
UCC5390ECD	LIFEBUY	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	53X0E	
UCC5390ECDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	53X0E	Samples
UCC5390ECDWV	LIFEBUY	SOIC	DWV	8	64	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	5390EC	
UCC5390ECDWVR	ACTIVE	SOIC	DWV	8	1000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	5390EC	Samples
UCC5390SCD	LIFEBUY	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	53X0S	
UCC5390SCDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	53X0S	Samples

(1) The marketing status values are defined as follows:  
**ACTIVE:** Product device recommended for new designs.



**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSELETE:** TI has discontinued the production of the device.

<sup>(2)</sup> **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

**Important Information and Disclaimer:**The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

**OTHER QUALIFIED VERSIONS OF UCC5350, UCC5390 :**

- Automotive : [UCC5350-Q1](#), [UCC5390-Q1](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

**TAPE AND REEL INFORMATION**

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
UCC5310MCDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
UCC5310MCDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
UCC5310MCDWVR	SOIC	DWV	8	1000	330.0	16.4	12.05	6.15	3.3	16.0	16.0	Q1
UCC5320ECDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
UCC5320SCDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
UCC5320SCDWVR	SOIC	DWV	8	1000	330.0	16.4	12.05	6.15	3.3	16.0	16.0	Q1
UCC5350MCDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
UCC5350MCDWVR	SOIC	DWV	8	1000	330.0	16.4	12.05	6.15	3.3	16.0	16.0	Q1
UCC5390ECDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
UCC5390ECDWVR	SOIC	DWV	8	1000	330.0	16.4	12.05	6.15	3.3	16.0	16.0	Q1
UCC5390SCDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
UCC5310MCDR	SOIC	D	8	2500	350.0	350.0	43.0
UCC5310MCDR	SOIC	D	8	2500	356.0	356.0	35.0
UCC5310MCDWVR	SOIC	DWV	8	1000	350.0	350.0	43.0
UCC5320ECDR	SOIC	D	8	2500	350.0	350.0	43.0
UCC5320SCDR	SOIC	D	8	2500	350.0	350.0	43.0
UCC5320SCDWVR	SOIC	DWV	8	1000	350.0	350.0	43.0
UCC5350MCDR	SOIC	D	8	2500	356.0	356.0	35.0
UCC5350MCDWVR	SOIC	DWV	8	1000	350.0	350.0	43.0
UCC5390ECDR	SOIC	D	8	2500	350.0	350.0	43.0
UCC5390ECDWVR	SOIC	DWV	8	1000	350.0	350.0	43.0
UCC5390SCDR	SOIC	D	8	2500	350.0	350.0	43.0

**TUBE**


\*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
UCC5310MCD	D	SOIC	8	75	505.46	6.76	3810	4
UCC5310MCD	D	SOIC	8	75	506.6	8	3940	4.32
UCC5310MCDWV	DWV	SOIC	8	64	505.46	13.94	4826	6.6
UCC5320ECD	D	SOIC	8	75	505.46	6.76	3810	4
UCC5320SCD	D	SOIC	8	75	505.46	6.76	3810	4
UCC5320SCDWV	DWV	SOIC	8	64	505.46	13.94	4826	6.6
UCC5350MCD	D	SOIC	8	75	506.6	8	3940	4.32
UCC5350MCD	D	SOIC	8	75	505.46	6.76	3810	4
UCC5350MCDWV	DWV	SOIC	8	64	505.46	13.94	4826	6.6
UCC5350SBD	D	SOIC	8	75	506.6	8	3940	4.32
UCC5350SBD	D	SOIC	8	75	505.46	6.76	3810	4
UCC5390ECD	D	SOIC	8	75	505.46	6.76	3810	4
UCC5390ECDWV	DWV	SOIC	8	64	505.46	13.94	4826	6.6
UCC5390SCD	D	SOIC	8	75	505.46	6.76	3810	4



D0008A

# PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



4214825/C 02/2019

## NOTES:

- Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- This drawing is subject to change without notice.
- This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed  $.006$  [0.15] per side.
- This dimension does not include interlead flash.
- Reference JEDEC registration MS-012, variation AA.

# EXAMPLE BOARD LAYOUT

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE  
 EXPOSED METAL SHOWN  
 SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE  
BASED ON .005 INCH [0.125 MM] THICK STENCIL  
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

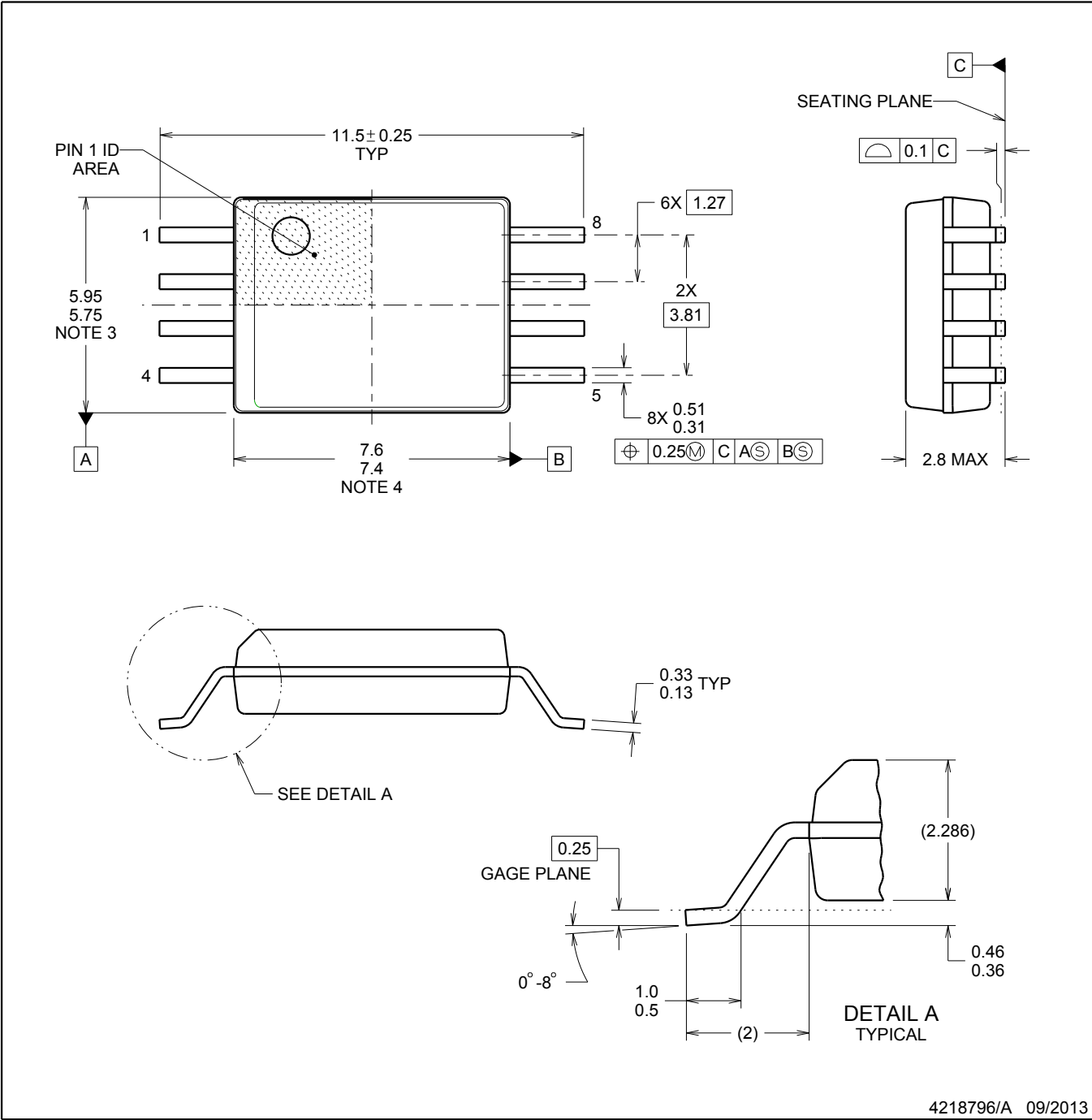
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.



DWV0008A

SOIC - 2.8 mm max height

SOIC



4218796/A 09/2013

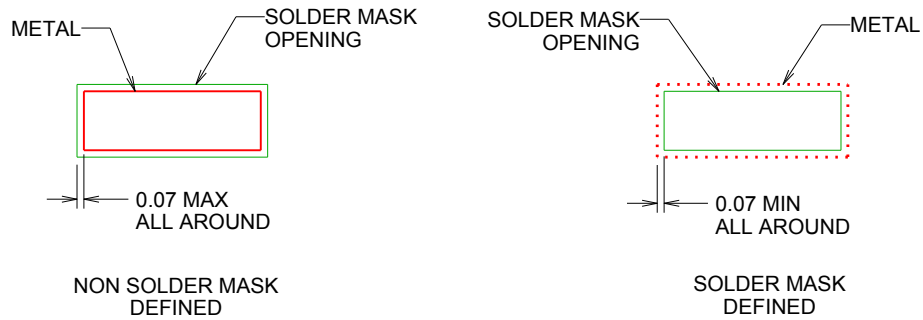
NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.





LAND PATTERN EXAMPLE  
9.1 mm NOMINAL CLEARANCE/CREEPAGE  
SCALE:6X

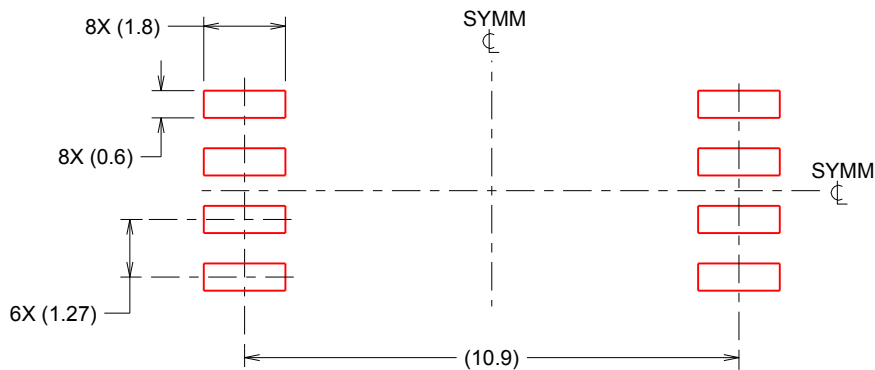


SOLDER MASK DETAILS

4218796/A 09/2013

NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE  
 BASED ON 0.125 mm THICK STENCIL  
 SCALE:6X

4218796/A 09/2013

NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.

## 重要なお知らせと免責事項

TI は、技術データと信頼性データ(データシートを含みます)、設計リソース(リファレンス・デザインを含みます)、アプリケーションや設計に関する各種アドバイス、Web ツール、安全性情報、その他のリソースを、欠陥が存在する可能性のある「現状のまま」提供しており、商品性および特定目的に対する適合性の黙示保証、第三者の知的財産権の非侵害保証を含むいかなる保証も、明示的または黙示的にかかわらず拒否します。

これらのリソースは、TI 製品を使用する設計の経験を積んだ開発者への提供を意図したものです。(1) お客様のアプリケーションに適した TI 製品の選定、(2) お客様のアプリケーションの設計、検証、試験、(3) お客様のアプリケーションに該当する各種規格や、その他のあらゆる安全性、セキュリティ、規制、または他の要件への確実な適合に関する責任を、お客様のみが単独で負うものとし、

上記の各種リソースは、予告なく変更される可能性があります。これらのリソースは、リソースで説明されている TI 製品を使用するアプリケーションの開発の目的でのみ、TI はその使用をお客様に許諾します。これらのリソースに関して、他の目的で複製することや掲載することは禁止されています。TI や第三者の知的財産権のライセンスが付与されている訳ではありません。お客様は、これらのリソースを自身で使用した結果発生するあらゆる申し立て、損害、費用、損失、責任について、TI およびその代理人を完全に補償するものとし、TI は一切の責任を拒否します。

TI の製品は、[TI の販売条件](#)、または [ti.com](#) やかかる TI 製品の関連資料などのいずれかを通じて提供する適用可能な条項の下で提供されています。TI がこれらのリソースを提供することは、適用される TI の保証または他の保証の放棄の拡大や変更を意味するものではありません。

お客様がいかなる追加条項または代替条項を提案した場合でも、TI はそれらに異議を唱え、拒否します。

郵送先住所 : Texas Instruments, Post Office Box 655303, Dallas, Texas 75265  
Copyright © 2024, Texas Instruments Incorporated